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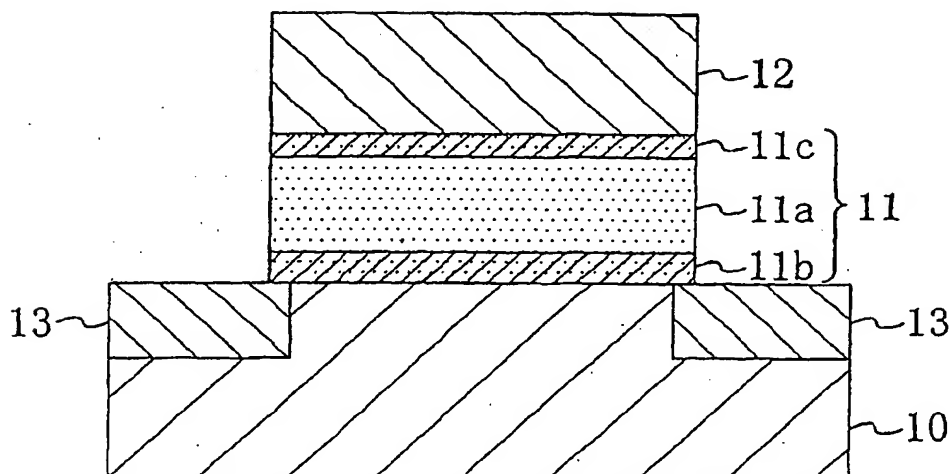
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(54) SEMICONDUCTOR DEVICE AND ITS MANUFACTURING METHOD

(57) A gate electrode **12** is formed on a silicon substrate **10** via a gate insulating film **11**. The gate insulating film **11** includes a high dielectric constant film **11a** made

of a hafnium oxide film containing silicon, and a lower barrier film **11b** formed below the high dielectric constant film **11a** and made of a silicon oxynitride film containing hafnium.

Fig. 1



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Description

TECHNICAL FIELD

[0001] The present invention relates to a semiconductor device and a method for producing the same, in particular, a high dielectric constant film used for a gate insulating film.

BACKGROUND ART

[0002] With recent technological advance with respect to high integration and high speed in semiconductor devices, miniaturization of MOSFETs has been under development. When the thickness of a gate insulating film is being reduced to achieve the miniaturization, problems such as an increase of a gate leak current due to tunneling current are caused. In order to suppress this problem, there has been research on an approach to increase a physical thickness while realizing a small SiO₂ equivalent thickness (hereinafter, referred to as "EOT") by using gate insulating films made of high dielectric constant material such as hafnium oxide (HfO₂) and zirconium oxide (ZrO₂) (hereinafter, referred to as "high-k gate insulating films").

[0003] For example, a method for forming a conventional high-k gate insulating film described in USP6013553 is as follows. First, an oxide layer such as a SiO₂ layer is formed on a silicon substrate, and then a metal film made of zirconium or hafnium is deposited on the oxide layer by sputtering or plasma CVD. Thereafter, the metal film is subjected to an oxynitridation treatment with gas such as NO to form a high-k gate insulating film made of zirconium oxynitride (ZrO_xN_y) or hafnium oxynitride (HfO_xN_y).

[0004] However, in the conventional high-k gate insulating film, when heat history is applied by a high temperature treatment during the production process, the high dielectric constant material constituting the gate insulating film is crystallized, so that the electrical conductivity via the resultant crystal grain boundaries or the defect level increases leak current. That is to say, the thermal stability of the conventional high-k gate insulating film is insufficient.

DISCLOSURE OF INVENTION

[0005] Therefore, with the foregoing in mind, it is an object of the present invention to provide a semiconductor device employing a thermally stable gate insulating film having a high relative dielectric constant.

[0006] In order to achieve the object, a semiconductor device of the present invention includes a gate insulating film formed on a substrate; and a gate electrode formed on the gate insulating film, and the gate insulating film includes a high dielectric constant film containing a metal, oxygen and silicon; and a lower barrier film formed below the high dielectric constant film and con-

taining the metal, oxygen, silicon and nitrogen.

[0007] According to the semiconductor of the present invention, the high dielectric constant film constituting the gate insulating film contains silicon, so that the high dielectric constant film is prevented from being crystallized by a high temperature treatment in the production process (e.g., a heat treatment for activating impurities at about 900°C). Therefore, in a finished semiconductor device, the high dielectric constant film remains mostly amorphous, so that leak current can be suppressed from occurring in the high-k gate insulating film. Consequently, the thermal stability of the high-k gate insulating film can be improved, and therefore a semiconductor device having excellent heat resistance can be realized, and the process margin in the production of a semiconductor device can be increased.

[0008] According to the semiconductor of the present invention, the lower barrier film is present below the high dielectric constant film in the gate insulating film, so that the high dielectric constant film can be prevented from reacting with the substrate. Moreover, the lower barrier film contains the same metal as in the high dielectric constant film, so that the relative dielectric constant of the lower barrier film can be increased, and thus the relative dielectric constant of the entire gate insulating film can be increased.

[0009] In the semiconductor device of the present invention, it is preferable that the gate insulating film includes an upper barrier film formed above the high dielectric constant film, and the upper barrier film contains the metal, oxygen and nitrogen.

[0010] This prevents the gate electrode material and the high dielectric constant film material from being diffused to each other. Moreover, the upper barrier film contains the same metal as in the high dielectric constant film, so that the relative dielectric constant of the upper barrier film can be increased, and thus the relative dielectric constant of the gate insulating film as a whole can be increased.

[0011] In the semiconductor device of the present invention, it is preferable to satisfy

$$0.23 \leq y/(x+y) \leq 0.90$$

when the composition of the high dielectric constant film is expressed as M_xSi_yO, where M, O and Si represent the metal, oxygen and silicon, respectively, and x > 0 and y > 0.

[0012] This ensures the thermal stability of the high-k gate insulating film against a heat treatment at about 900°C while keeping the relative dielectric constant of the high-k gate insulating film sufficient.

[0013] In the semiconductor device of the present invention, it is preferable to satisfy

$$0.23 \leq y/(x+y) \leq 0.30$$

when the composition of the high dielectric constant film is expressed as $M_xSi_yO_z$, where M, O and Si represent the metal, oxygen and silicon, respectively, and $x > 0$ and $y > 0$.

[0014] This ensures the thermal stability of the high-k gate insulating film against a heat treatment at about 900°C while keeping the reliability life of the high-k gate insulating film sufficient.

[0015] In the semiconductor device of the present invention, it is preferable to satisfy

$$x/(x+y) \geq 0.10$$

when the metal is hafnium or zirconium, and the composition of the lower barrier film is expressed as $M_xSi_yON_z$, where M, O, Si and N represent the metal, oxygen, silicon and nitrogen, respectively, and $x > 0$ and $y > 0$.

[0016] This ensures that the relative dielectric constant of the lower barrier film can be increased.

[0017] In the semiconductor device of the present invention, the gate electrode may be a metal gate electrode.

[0018] A first method for producing a semiconductor device of the present invention includes the steps of forming a high dielectric constant film containing a metal, oxygen and a predetermined substance on a substrate; performing a heat treatment with respect to the high dielectric constant film to diffuse silicon from the side of the substrate into the high dielectric constant film, thereby forming a silicon-containing high dielectric constant film; and forming a conductive film for serving as a gate electrode on the silicon-containing high dielectric constant film.

[0019] According to the first method for producing a semiconductor device, a predetermined substance can be desorbed from the high dielectric constant film by performing a heat treatment with respect to the high dielectric constant film containing the predetermined substance, so that silicon is diffused in the high dielectric constant film through the thus formed vacancies and thus a silicon-containing high dielectric constant film can be formed. Therefore, silicon can be contained in the high dielectric constant film efficiently, and the vacancies eventually disappear, so that the silicon-containing high dielectric constant film can become dense. The silicon-containing high dielectric constant film hardly is crystallized by a high temperature treatment in the production process, so that the silicon-containing high dielectric constant film remains mostly amorphous after a device is complete. As a result, leak current can be suppressed from occurring in the gate insulating film including the silicon-containing high dielectric constant film, that is, the high-k gate insulating film. Consequently, the thermal stability of the high-k gate insulating film can be improved, and therefore a semiconductor device having excellent heat resistance can be realized, and the proc-

ess margin in the production of a semiconductor device can be increased.

[0020] In the first semiconductor method of the present invention, it is preferable the predetermined substance is hydrogen.

[0021] This ensures that silicon can be diffused in the high dielectric constant film.

[0022] It is preferable that the first semiconductor method includes forming an insulating film containing silicon, nitrogen and the predetermined substance on the substrate before the step of forming the high dielectric constant film; and that the step of performing a heat treatment with respect to the high dielectric constant film comprises diffusing silicon contained in the insulating film into the high dielectric constant film, and forming a lower barrier film by diffusing the metal contained in the high dielectric constant film into the insulating film.

[0023] This ensures that silicon can be diffused in the high dielectric constant film. Furthermore, the high dielectric constant film or the silicon-containing high dielectric constant film can be prevented from reacting with the substrate. Moreover, the lower barrier film contains the same metal as in the silicon-containing high dielectric constant film, so that the relative dielectric constant of the lower barrier film can be increased, and thus the relative dielectric constant of the gate insulating film as a whole can be increased.

[0024] In the first method for producing a semiconductor device, it is preferable that the step of forming a high dielectric constant film comprises forming a high dielectric constant film by CVD employing a source precursor containing the metal and the predetermined substance.

[0025] This ensures that a high dielectric constant film containing the predetermined substance is formed.

[0026] In the first method for producing a semiconductor device, it is preferable that the step of forming the high dielectric constant film includes forming the high dielectric constant film by CVD employing a source precursor containing the metal and a source gas containing the predetermined substance.

[0027] This ensures that a high dielectric constant film containing the predetermined substance is formed.

[0028] In the first method for producing a semiconductor device, it is preferable that the step of forming the high dielectric constant film includes forming the high dielectric constant film by PVD employing a target containing the metal in an atmosphere containing the predetermined substance.

[0029] This ensures that a high dielectric constant film containing the predetermined substance is formed.

[0030] A second method for producing a semiconductor device of the present invention includes the steps of forming a high dielectric constant film containing a metal, oxygen and hydrogen on a substrate; performing a heat treatment with respect to the high dielectric constant film to diffuse silicon from the side of the substrate into the high dielectric constant film, thereby forming a silicon-containing high dielectric constant film; and form-

ing a conductive film for serving as a gate electrode on the silicon-containing high dielectric constant film.

[0031] According to the second method for producing a semiconductor device, hydrogen can be desorbed from the high dielectric constant film by performing a heat treatment with respect to the high dielectric constant film containing hydrogen, so that silicon is diffused in the high dielectric constant film through the thus formed vacancies and thus a silicon-containing high dielectric constant film can be formed. Therefore, silicon can be contained in the high dielectric constant film efficiently, and the vacancies eventually disappear, so that the silicon-containing high dielectric constant film can become dense. The silicon-containing high dielectric constant film hardly is crystallized by a high temperature treatment in the production process, so that the silicon-containing high dielectric constant film remains mostly amorphous after a device is complete. As a result, leak current can be suppressed from occurring in the gate insulating film including the silicon-containing high dielectric constant film, that is, the high-k gate insulating film. Consequently, the thermal stability of the high-k gate insulating film can be improved, and therefore a semiconductor device having excellent heat resistance can be realized, and the process margin in the production of a semiconductor device can be increased.

[0032] It is preferable that the second method for producing a semiconductor device includes forming an insulating film containing silicon, nitrogen and hydrogen on the substrate before the step of forming the high dielectric constant film; and that the step of performing a heat treatment with respect to the high dielectric constant film includes diffusing silicon contained in the insulating film into the high dielectric constant film, and forming a lower barrier film by diffusing the metal contained in the high dielectric constant film into the insulating film.

[0033] This ensures that silicon can be diffused in the high dielectric constant film. Furthermore, the high dielectric constant film or the silicon-containing high dielectric constant film can be prevented from reacting with the substrate. Moreover, the lower barrier film contains the same metal as in the silicon-containing high dielectric constant film, so that the relative dielectric constant of the lower barrier film can be increased, and thus the relative dielectric constant of the entire gate insulating film can be increased.

[0034] In the second method for producing a semiconductor device, it is preferable that the step of forming the high dielectric constant film includes forming the high dielectric constant film by CVD employing a source precursor containing the metal and hydrogen.

[0035] Thus ensures that a high dielectric constant film containing hydrogen can be formed.

[0036] In the second method for producing a semiconductor device, it is preferable that the step of forming the high dielectric constant film includes forming the high dielectric constant film by CVD employing a source

precursor containing the metal and a source gas containing hydrogen.

[0037] Thus ensures that a high dielectric constant film containing hydrogen can be formed.

[0038] In the second method for producing a semiconductor device, it is preferable that the step of forming the high dielectric constant film includes forming the high dielectric constant film by PVD employing a target containing the metal in an atmosphere containing hydrogen.

[0039] Thus ensures that a high dielectric constant film containing hydrogen can be formed.

[0040] In the first or the method for producing a semiconductor device; it is preferable that the metal is hafnium or zirconium.

[0041] This ensures that the relative dielectric constant of the silicon-containing high dielectric constant film can be increased.

[0042] In the first or the second method for producing a semiconductor device, it is preferable that the method includes the step of forming an upper barrier by nitriding a surface of the silicon-containing high dielectric constant film between the step of performing a heat treatment with respect to the high dielectric constant film and the step of forming a conductive film.

[0043] This prevents the gate electrode material and the high dielectric constant film material from being diffused to each other. Moreover, the upper barrier film contains the same metal as in the high dielectric constant film, so that the relative dielectric constant of the upper barrier film can be increased, and thus the relative dielectric constant of the entire gate insulating film can be increased.

[0044] In the first or the second method for producing a semiconductor device, it is preferable that the method includes the step of forming an upper barrier by nitriding a surface of the high dielectric constant film between the step of forming a high dielectric constant film and the step of performing a heat treatment with respect to the high dielectric constant film.

[0045] This prevents the gate electrode material and the high dielectric constant film material from being diffused to each other. Moreover, the upper barrier film contains the same metal as in the high dielectric constant film, so that the relative dielectric constant of the upper barrier film can be increased, and thus the relative dielectric constant of the entire gate insulating film can be increased.

[0046] In the first or the second method for producing a semiconductor device, it is preferable that the temperature for the heat treatment in the step of performing the heat treatment with respect to the high dielectric constant film is 600°C or more and 850°C or less.

[0047] This ensures that the predetermined substance or hydrogen can be desorbed from the high dielectric constant film, and that silicon can be diffused in the high dielectric constant film.

[0048] In the first or the second method for producing

a semiconductor device, it is preferable to satisfy $T \leq 6.69 \cdot y/(x+y) + 749.4$, when the composition of the silicon-containing high dielectric constant film is expressed as $M_xSi_yO_z$, where M, O and Si represent the metal, oxygen and silicon, respectively, and $x > 0$ and $y > 0$, and the maximum temperature in the production process is expressed as $T [^{\circ}C]$.

[0049] This ensures the thermal stability of the high-k gate insulating film having the silicon-containing high dielectric constant film.

[0050] In this case, it is preferable that the gate electrode is made of a material containing silicon, and $y/(x+y) \leq 0.30$ is satisfied.

[0051] This enables a sufficient reliability life for the high-k gate insulating film having the silicon-containing high dielectric constant film.

[0052] In the first or the second method for producing a semiconductor device, it is preferable that the gate electrode is a metal gate electrode, and the method includes the step of performing a heat treatment with respect to the substrate after the step of forming a conductive film.

[0053] This allows the defects in the high-k gate insulating film having the silicon-containing high dielectric constant film to be reduced further.

BRIEF DESCRIPTION OF THE DRAWINGS

[0054]

Figure 1 is a cross-sectional view of a semiconductor device according to a first embodiment of the present invention.

Figure 2 is a graph showing the relationship between the amount of Si added to HfO_2 and the crystallization temperature of HfO_2 and the temperature that guarantees thermal stability of HfO_2 .

Figure 3 is a diagram showing the allowable range of the composition of Hf silicate that can maintain the thermal stability obtained corresponding to various maximum process temperatures.

Figure 4 is a graph showing the relationship between the amount of Si added to a HfO_2 film and the relative dielectric constant of the HfO_2 film.

Figure 5 is a graph showing the relationship between the amount of Si added to a HfO_2 film and the reliability life of the HfO_2 film.

Figure 6 is a graph showing the relationship between the amount of Si added to a HfO_2 film and the thermal stability and the reliability of the HfO_2 film.

Figures 7A to 7C are cross-sectional views showing the processes in a method for producing a semiconductor device according to a second embodiment of the present invention.

Figures 8A to 8C are cross-sectional views showing the processes in a method for producing the semiconductor device according to the second embodi-

ment of the present invention.

Figures 9A to 9D are views illustrating the behavior resulted from PDA in the method for producing the semiconductor device according to the second embodiment of the present invention.

Figure 10 is a graph showing the results of measurement by TDS regarding hydrogen being desorbing from the HfO_2 film due to a heat treatment.

Figure 11 is a graph showing the results of C-V measurement after a heat treatment with respect to a H-containing HfO_2 film formed by CVD using Hf-t-butoxide in the method for producing a semiconductor device according to the second embodiment of the present invention.

Figure 12 is a graph showing the result of C-V measurement after a heat treatment with respect to a H-free HfO_2 film formed by CVD using a source that does not contain hydrogen as a comparative example.

Figure 13 is a graph showing the results of a comparison in the thermal stability between the case where the H-containing HfO_2 film (the second embodiment of the present invention) is used and the case where the H-free HfO_2 film (comparative example) is used in a MOS capacitor having a layered structure of Si substrate / SiN film / HfO_2 film / polysilicon film.

Figure 14 is a graph showing the relationship between the physical thickness of a HfO_2 film that has just formed and the leak current after a MOS capacitor is complete in the case where PDA in the method for producing a semiconductor device of the second embodiment of the present invention is performed with respect to the HfO_2 film, which is an insulating film of the MOS capacitor.

BEST MODE FOR CARRYING OUT THE INVENTION

First Embodiment

[0055] Hereinafter, a semiconductor device of a first embodiment of the present invention, more specifically, a MISFET will be described with reference to the accompanying drawings.

[0056] Figure 1 shows the cross-sectional structure of a semiconductor device of a first embodiment.

[0057] As shown in Figure 1, a gate electrode 12 is formed on a silicon substrate 10 via a gate insulating film 11. An impurity diffusion layer 13 serving as a source region or a drain region is formed on both sides of the gate electrode 12 in the silicon substrate 10. The gate insulating film 11 includes a high dielectric constant film 11a made of insulative metal oxide, a lower barrier film 11b formed below the high dielectric constant film 11a, and an upper barrier film 11c formed above the high dielectric constant film 11a.

[0058] More specifically, the high dielectric constant film 11a is formed of a substance in which silicon is con-

tained in hafnium oxide (HfO_2) having a high relative dielectric constant, that is, a silicon-containing hafnium oxide ($\text{Hf}_x\text{Si}_y\text{O}_2$, where $x > y > 0$). The lower barrier film 11b for preventing a reaction between the silicon substrate 10 and the high dielectric constant film 11a is made of, for example, a silicon oxynitride film containing hafnium. The upper barrier film 11c for preventing a reaction between the high dielectric constant film 11a and the gate electrode 12 is made of, for example, a silicon-containing hafnium oxide film containing nitrogen. That is to say, the lower barrier film 11b and the upper barrier film 11c are high dielectric constant barrier films. The gate electrode 12 is made of, for example, a polysilicon film doped with phosphorus.

[0059] The high dielectric constant film 11a may contain nitrogen. When the physical thickness of the gate insulating film 11 is about 4 nm, the physical thickness of the high dielectric constant film 11a is about 2 nm, the physical thickness of the lower barrier film 11b is slightly smaller than 1 nm, and the physical thickness of the upper barrier film 11c is slightly larger than 1 nm. All of the high dielectric constant film 11a, the lower barrier film 11b, and the upper barrier film 11c are amorphous.

[0060] In this embodiment, silicon is contained in the HfO_2 film that serves as the high dielectric constant film 11a for the purpose of ensuring the thermal stability of the high dielectric constant film 11a. In other words, the high dielectric constant film 11a containing silicon is hardly crystallized (or is only partially crystallized and remains amorphous) when being subjected to a heat treatment at a high temperature, so that an increase of leak current due to crystal grain boundaries or defect level can be suppressed. Hereinafter, this embodiment will be described more specifically with reference to the accompanying drawings.

[0061] Figure 2 shows the relationship between the amount of silicon (Si) added to HfO_2 and the crystallization temperature of HfO_2 and the thermal stability guarantee temperature of HfO_2 . The crystallization temperature refers to the temperature at which an amorphous state started to change into a crystalline state. In other words, since a change of the state starts at the crystallization temperature, the entire substance (HfO_2) is not necessarily crystallized immediately even if the temperature exceeds the crystallization temperature.

[0062] In Figure 2, the horizontal axis shows the ratio X_1 (% representation) of the number of Si atoms contained in HfO_2 per unit volume (hereinafter, referred to as "Si concentration") to the sum of the Si concentration and the number of Hf atoms contained in HfO_2 per unit volume (hereinafter, referred to as "Hf concentration"). In other words, the far left end in the horizontal axis ($X_1 = (\text{Si concentration} / (\text{Si concentration} + \text{Hf concentration})) \times 100 = 0\%$) indicates HfO_2 that contains no Si, and the far right end in the horizontal axis ($X_1 = (\text{Si concentration} / (\text{Si concentration} + \text{Hf concentration})) \times 100 = 100\%$) indicates SiO_2 that contains no Hf. The vertical axis shows the temperature.

[0063] As shown in Figure 2, the crystallization temperature and the thermal stability guarantee temperature of HfO_2 increase with the ratio X_1 , that is, the amount of added Si. In other words, the addition of silicon to HfO_2 increases the thermal stability of HfO_2 . This is because an increase of the Si amount makes it easy that Si-containing HfO_2 , that is, a Hf silicate material remains amorphous, and as a result, the entire HfO_2 film hardly is crystallized and remains amorphous.

[0064] Herein, the thermal stability guarantee temperature refers to the annealing temperature at which a drastic increase of leak current starts to occur in an insulating film made of HfO_2 when an annealing treatment is performed with respect to a MOS capacitor structure having the insulating film for 30 seconds in N_2 gas at 1 atm with a rapid thermal process (RTP) apparatus. Therefore, at temperatures below the thermal stability guarantee temperature, the leak current and the capacitance in the MOS capacitor structure employing the Si-containing HfO_2 film indicates an ideal value. On the other hand, at temperatures above the thermal stability guarantee temperature, the leak current in the MOS capacitor structure increases by about three orders due to a drastic increase of defects locally occurring in the Si-containing HfO_2 film. At this point, the capacitance in an accumulation state in a C-V (capacitance-voltage) measurement diverges, and therefore it becomes impossible to measure the capacitance of the MOS capacitor. In other words, at temperatures above the thermal stability guarantee temperature, the MOS capacitor structure employing the Si-containing HfO_2 film cannot serve as a capacitor.

[0065] When the ratio X_1 is 70% or more, the substantially entire Si-containing HfO_2 film can be kept amorphous even at high temperatures, so that even if the film is subjected to a high temperature process at 1200°C , leak current can be suppressed. If the ratio X_1 is at least 23%, the crystals produced when the Si-containing HfO_2 film is crystallized are microcrystalline, and the film as a whole is predominantly in the amorphous state. Therefore, leak current can be suppressed even if the film is subjected to a high temperature process of 900°C . Herein, the case where the material to be used is mostly amorphous, or the case where the material to be used contains crystallites to the extent that makes substantially no influence on the thermal stability, that is, the heat resistance, is also regarded as being amorphous.

[0066] As shown in Figure 2, the straight line showing the range of the process temperature that can be used in the process for producing a semiconductor device and the range of the Si concentration in the Si-containing HfO_2 film can be defined as $T = 6.69 \cdot X_1 + 749.4$, where X_1 represents the Si concentration / (Si concentration + Hf concentration) $\times 100$ and $T [^\circ\text{C}]$ represents the thermal stability guarantee temperature (more specifically, when a polysilicon electrode is used). In other words, it is necessary that the process temperature and

the Si concentration are in the range below $T = 6.69 \cdot X_1 + 749.4$. More specifically, when the value of X_1 , that is, the composition of the Si-containing HfO_2 is determined, the process temperature has to be in the temperature range of not more than the thermal stability guarantee temperature T corresponding to the predetermined value of X_1 . On the other hand, when the maximum temperature of the process is determined, it is necessary to select a Si-containing HfO_2 film, that is, a Hf silicate film to which Si is added such that X_1 is larger than a value of X_1 when the maximum temperature is used as the thermal stability guarantee temperature T . In the case of the structure of the semiconductor device of this embodiment shown in Figure 1, the Si concentration can be determined as described above, with respect to, for example, either the entire gate insulating film 11 or a region about 2nm below the interface with the gate electrode 12 in the gate insulating film 11 in view of a contact with the gate electrode 12.

[0067] Figure 3 shows the allowable range of the composition (X_1) of Hf silicate that can ensure the thermal stability, which was obtained corresponding to various maximum process temperatures based on the relationship (experiment results) shown in Figure 2. As shown in Figure 3, for example, when the maximum process temperature is about 900°C (e.g., in the process in which polysilicon is used as the electrode material), X_1 should be at least 23% in order to prevent a drastic increase of leak current due to defects or the like and ensures the thermal stability.

[0068] Figure 4 shows the relationship between the amount of Si added to the HfO_2 film and the relative dielectric constant of the HfO_2 film. In Figure 4, the upper horizontal axis shows $X_1 = (\text{Si concentration} / (\text{Si concentration} + \text{Hf concentration})) \times 100$ as described above, which indicates the Si amount. The lower horizontal axis shows $X_2 = (\text{Hf concentration} / (\text{Si concentration} + \text{Hf concentration})) \times 100$ as described above, which indicates the Hf amount. The vertical axis shows the relative dielectric constant of the HfO_2 film. □ shows the value obtained by an actual measurement of the relative dielectric constant.

[0069] As shown in Figure 4, when X_1 is 0% (that is, when the film is the HfO_2 film, which contains no Si), the relative dielectric constant of the HfO_2 film is about 24, which is the maximum. The relative dielectric constant decreases as the Si amount in the HfO_2 film increases, but the relative dielectric constant is substantially constantly about 11 when X_1 is between 30% and 90%. When the Si amount in the HfO_2 film further increases and exceeds 90%, the relative dielectric constant gradually decreases again, and the relative dielectric constant is about 3.9 when X_1 is 100% (that is, when the film is the SiO_2 film, which contains no Hf). Therefore, when X_1 is 90% or less, that is, when X_2 is 10% or more, a Hf silicate film having a comparatively high and stable relative dielectric constant can be realized.

[0070] According to the results shown in Figures 2 to

4 described above, it is important to set $X_1 = (\text{Si concentration} / (\text{Si concentration} + \text{Hf concentration})) \times 100$ in the high dielectric constant film 11a made of silicon-containing HfO_2 to 23% or more and 90% or less in order that the high dielectric constant film 11a (which may be a stacked structure of a combination of the high dielectric constant film 11a, the lower barrier film 11b and/or the upper barrier film 11c, instead of the high dielectric constant film 11a) has the thermal stability while having a high relative dielectric constant.

[0071] $X_1 = (\text{Si concentration} / (\text{Si concentration} + \text{Hf concentration})) \times 100$ has the same meaning as $(y / (x + y)) \times 100$ when the composition of the high dielectric constant 11a is represented as $\text{Hf}_x\text{Si}_y\text{O}$ (where $x > 0$, and $y > 0$). Similarly, $X_2 = (\text{Hf concentration} / (\text{Si concentration} + \text{Hf concentration})) \times 100$ has the same meaning as $(x / (x + y)) \times 100$. X_1 and X_2 show the relationship between the Si concentration and the Hf concentration, so that also when Hf silicate to be used contains N in the form of Hf silicate nitride, or when it contains other elements such as Cl, F and H, the above description employing X_1 and X_2 is effective.

[0072] Figure 5 shows the relationship between the amount of Si added to the HfO_2 film and the reliability life of the HfO_2 film (period of time until breakdown occurs). In Figure 5, the upper horizontal axis shows $X_1 = (\text{Si concentration} / (\text{Si concentration} + \text{Hf concentration})) \times 100$ as described above, which indicates the Si amount. The lower horizontal axis shows $X_2 = (\text{Hf concentration} / (\text{Si concentration} + \text{Hf concentration})) \times 100$ as described above, which indicates the Hf amount. The vertical axis shows the reliability life of the HfO_2 film. □ shows the value obtained by an actual measurement of the reliability life.

[0073] More specifically, various samples of MOS capacitors having Hf silicate films having different compositions are prepared, and a TDDB (time dependent dielectric breakdown measurement) test is performed to estimate the long term reliability life of the Hf silicate films under the conditions of an incidence of failure of 100 ppm, an insulating film area (MOS area) of 0.1 cm², a temperature of 100°C, an applied voltage $V_G = -1V$, and EOT (SiO_2 equivalent thickness) = 1.5 nm. The results are shown in Figure 5. Herein, the composition of the Hf silicate in each sample varies in the range from SiO_2 , which contains no Hf, to HfO_2 , which contains no Si. Each sample is formed on a p-type substrate, and a constant negative stress voltage is applied to the electrodes, setting 0 V on the substrate side.

[0074] More specifically, the insulating film area of each sample used in the TDDB test is in the range from $3 \times 10^{-7} \text{ cm}^2$ to $5 \times 10^{-5} \text{ cm}^2$. To obtain the reliability life at an insulating film area of 0.1 cm², the following equation based on the assumption that defects in the insulating film are distributed according to the Poisson distribution was used:

[0075] The reliability life of the insulating film area 1 = the reliability life of the insulating film area 2 ×

(insulating film area 2 / insulating film area 1) $^{(1/\beta)}$, where β is a Weibull gradient. The temperature during the TDDB test is in the range from room temperature to 100°C. To obtain the reliability life at a temperature of 100°C, activation energy of the reliability life obtained in advance with respect to a temperature change was used. To obtain the reliability life at an incidence of failure of 100 ppm, a Weibull gradient β was obtained based on a Weibull plot obtained by the TDDDB test, and then the approximate straight line of an intrinsic breakdown was extended. Furthermore, in the TDDDB test, V_G larger than 1 V as an absolute value is used, whereas in order to obtain the reliability life at $V_G = -1$ V, experiment data of the reliability life corresponding to a real electric field E_{ox} (real) that is obtained from an equation of $(V_G$ (at the time of the TDDDB test) $-V_{fb})/T_{ph}$, where V_{fb} is a flat band voltage, and T_{ph} is the physical thickness of the entire insulating film, were extended by the straight-line approximation.

[0076] According to the results shown in Figure 5 obtained using the above-described method, when X_1 (upper horizontal axis) is 30% or less, that is, when X_2 is 70% or more, the reliability life of the Hf silicate film is 10 years or more. The results shown in Figure 5 are those obtained by estimating the reliability life on the lower voltage side with respect to the real electric field E_{ox} (real). The results obtained by estimating the reliability life on the lower voltage side with respect to the V_G itself at the time of the TDDDB test or the effective electric field E_{ox} (effective) obtained by an equation of $(V_G$ (at the time of TDDDB test) $-V_{fb}) / EOT$ exhibit the similar tendency.

[0077] According to the results shown in Figures 2 to 4, when thermal stability and a high relative dielectric constant are targeted, it is preferable to set $X_1 = (\text{Si concentration} / (\text{Si concentration} + \text{Hf concentration})) \times 100$ to 23% or more and 90% or less. On the other hand, according to the results shown in Figure 5, when X_1 is 30% or less, the reliability life of 10 years or more can be obtained. That is to say, when reliability as well as thermal stability and a high relative dielectric constant are targeted, the preferable range of X_1 is 23% or more and 30% or less. However, in the case of a process that does not require a high temperature treatment after a gate insulating film is formed, such as a replacement gate process (process that allows a gate electrode to be formed after formation of source and drain regions by using a dummy gate), more specifically, in the case of a process that does not require a heat treatment at 750°C or more after a gate electrode is formed, it is sufficient to target only reliability, so that the preferable range of X_1 is 30% or less.

[0078] Figure 6 shows the relationship between the amount of Si added to the HfO_2 film and the thermal stability and the reliability of the HfO_2 film.

[0079] As shown in Figure 6, the preferable range of the structure (composition) of the high-k gate insulating film made of a HfO_2 film containing Si or the process

temperature can be divided roughly into three regions. To be specific, when only thermal stability is targeted, the preferable range is below $T = 6.69 \cdot X_1 + 749.4$. In order to obtain a comparatively high relative dielectric constant in the maximum process temperature of 900°C as well, X_1 has to be set to 23% or more and 90% or less. In the case of a process that does not require a high temperature treatment after a gate insulating film is formed, such as a case using a replacement gate, it is sufficient to target only reliability, so that it is sufficient to set X_1 to 30% or less. Furthermore, in a conventional Si process, when a high-k material is used as the gate insulating film material instead of SiON , and Poly-Si or SiGe or the like is used as the gate electrode material, that is, when annealing for activating impurities is performed at a comparatively high temperature after a gate insulating film is formed, it is necessary to target both thermal stability and reliability, so that the range that is below $T = 6.69 \cdot X_1 + 749.4$ and satisfies that X_1 is 30% or less is preferable. In this case, when the maximum process temperature is 900°C, X_1 has to be set to 23% or more and 30% or less. It should be noted that 900°C is a typical temperature in annealing for activating impurities contained in a source region, a drain region or an electrode.

[0080] As described above, according to the first embodiment, the high dielectric constant film 11a included in the gate insulating film 11 is a HfO_2 film containing silicon, so that the high electric constant film 11a can be prevented from being crystallized by a high temperature treatment in the production process. Therefore, in a finished semiconductor device, the high dielectric constant film 11a remains mostly amorphous, so that leak current can be suppressed from occurring in the gate insulating film 11, that is, the high-k gate insulating film. Consequently, the thermal stability of the gate insulating film 11 can be improved, so that a semiconductor device having excellent heat resistance can be realized, and the process margin in the production of the semiconductor device can be increased.

[0081] Furthermore, according to the first embodiment, the lower barrier film 11b containing silicon, nitrogen and oxygen is present below the high dielectric constant film 11a in the gate insulating film 11, so that the high dielectric constant film 11a and the silicon substrate 10 can be prevented from being reacted with each other. Herein, the lower barrier film 11b prevents the silicon substrate 10 from being oxidized by oxygen in the high dielectric constant film 11a. That is to say, when an oxide film having a relative dielectric constant substantially equal to that of a SiO_2 film is formed on the surface of the silicon substrate 10 as an interface layer, the relative dielectric constant of the gate insulating film 11 as a whole decreases significantly, and therefore the lower barrier film 11b is provided.

[0082] Furthermore, according to the first embodiment, the lower barrier film 11b contains the same metal as in the high dielectric constant film 11a specifically,

hafnium, so that the relative dielectric constant of the lower barrier film 11b can be higher than that of a regular silicon oxynitride film, so that the relative dielectric constant of the gate insulating film 11 as a whole can be made higher. More specifically, as shown in Figure 4, when hafnium is introduced into the lower barrier film 11b in a ratio of 10% or more with respect to silicon (that is $X_2 \geq 10\%$), so that the relative dielectric constant of the lower barrier film 11b can increase effectively. On the other hand, as shown in Figure 4, when the silicon content in the lower barrier film 11b is too large (more specifically, $X_1 \geq 90\%$), the relative dielectric constant decreases drastically. In other words, it is very effective to set the Hf concentration in the lower barrier film 11b to be higher than $X_2 = 0\%$ even to a slight extent in order to reduce the EOT of the entire gate insulating film 11.

[0083] Furthermore, according to the first embodiment, the upper barrier film 11c is present in a portion above the high dielectric constant film 11a in the gate insulating film 11, so that the material of the gate electrode 12 (polysilicon in this embodiment) is prevented from being mixed with the material of the high dielectric constant film 11a (e.g., hafnium) more than necessary, and thus a reduction of the relative dielectric constant of the gate insulating film 11 can be suppressed. In this case, the barrier effect of the upper barrier film 11c can be improved by allowing the upper barrier film 11c to contain nitrogen. The relative dielectric constant of the upper barrier film 11c can be increased by allowing the upper barrier film 11c to contain the same metal, hafnium, as the high dielectric constant film 11a, and thus the relative dielectric constant of the entire gate insulating film 11 can be increased.

[0084] In the first embodiment, it is preferable to set $X_1 = (\text{Si concentration} / (\text{Si concentration} + \text{Hf concentration})) \times 100$ in the high dielectric constant film 11a (which may be a stacked structure of a combination of the high dielectric constant film 11a, the lower barrier film 11b and/or the upper barrier film 11c instead of the high dielectric constant film 11a to 23% or more and 90% or less. By doing this, the relative dielectric constant of the high dielectric constant film 11a can be increased and even if a heat treatment at about 900°C is performed, the high dielectric constant film 11a can be suppressed from being crystallized, so that an increase of leak current due to defects or the like can be prevented. In other words, the thermal stability of the gate insulating film 11 can be ensured while the relative dielectric constant of the gate insulating film 11 is kept sufficient. In this case, it is more preferable to set X_1 in the high dielectric constant film 11a to 23% or more and 30% or less. By doing this, in addition to the above-described advantages, a sufficient reliability life of the high dielectric constant film 11a, that is, the gate insulating film 11 can be obtained. When the maximum process temperature is reduced to be significantly low by the use of a replacement gate or the like, merely setting X_1 to 30% or less ensures the thermal stability of the gate insulat-

ing film 11 while ensuring sufficient relative dielectric constant and reliability life of the gate insulating film 11. [0085] In the first embodiment, HfO_2 is used as the high dielectric constant material included in the gate insulating film 11, but instead of this material, ZrO_2 , TiO_2 , Ta_2O_5 , La_2O_3 , CeO_2 , Al_2O_3 , or BST (barium strontium titanium oxide) or the like can be used. Alternatively, ternary oxide such as $\text{Hf}_x\text{Al}_y\text{O}_2$, where $x > 0$, and $y > 0$ can be used. Alternatively, metal silicate in which Si atoms are contained in the above-listed metal oxides can be used.

[0086] In the first embodiment, the lower barrier film 11b and the upper barrier film 11c are provided, but there may be no need of providing the lower barrier film 11b and/or the upper barrier film 11c, depending on the selection of the material of the gate electrode 12.

[0087] In the first embodiment, a polysilicon electrode is used as the gate electrode 12, but instead of this, a so-called metal gate electrode made of a metal film such as a stacked film of a TiN film and a Al film (TiN film as the lower film), a Ta film, a TINT film or a TaN film can be used. If a metal film such as a TiN film or TaN film is used as the metal gate electrode material, Si or Ge can be mixed with the metal film.

Second Embodiment

[0088] Hereinafter, a method for producing a semiconductor device of a second embodiment of the present invention, specifically, a method for producing a MISFET will be described with reference to the accompanying drawings.

[0089] Figures 7A to 7C and 8A to 8C are cross-sectional views showing the processes of a method for producing a semiconductor device of the second embodiment.

[0090] First, as shown in Figure 7A, an insulating film for isolation (not shown) is formed on a p-type silicon (100) substrate 20, and a device forming region is segmented. Then, standard RCA cleaning and diluted HF cleaning are performed with respect to the surface of the silicon substrate 20. Thereafter, a silicon nitride film (Si_3N_4 film) 21A having a thickness of about 0.7 nm is formed on the silicon substrate 20 with NH_3 gas at a temperature of about 700°C. In this process, sufficient hydrogen is captured in the Si_3N_4 film 21A. The Si_3N_4 film 21A eventually becomes the lower barrier film 21 (see Figure 7C).

[0091] Next, as shown in Figure 7B, a hafnium oxide (HfO_2) film 22A having a thickness of about 5 nm is formed on the silicon substrate 20 by CVD (chemical vapor deposition) employing a source precursor containing hafnium. More specifically, nitrogen (N_2) gas as a carrier gas is allowed to pass through Hf-t-butoxide ($\text{C}_{16}\text{H}_{36}\text{HfO}_4$), which is a liquid Hf source, to bubble the Hf-t-butoxide to evaporate the Hf-t-butoxide. Then, a RTCVD (rapid thermal CVD) treatment is performed at a temperature of about 500 °C while the N_2 gas contain-

ing the evaporated Hf-t-butoxide and dry oxygen (O_2) gas as an oxidizing agent are supplied to a chamber in which the silicon substrate 20 (wafer) is placed, and thus a HfO_2 film 22A is formed.

[0092] In this process, the Si_3N_4 film 21A is oxidized by the O_2 gas as an oxidizing agent, and turns into a SiON film 21B. The SiON film 21B has barrier properties for preventing a reaction between the silicon substrate 20 and the HfO_2 film 22A and contains sufficient hydrogen. In this embodiment, after the Si_3N_4 film 21A is formed on the silicon substrate 20, the Si_3N_4 film 21A is oxidized during the formation of the HfO_2 film 22A to form the SiON film 21B. However, without forming the Si_3N_4 film 21A, the SiON film 21B can be directly formed by nitriding the surface of the silicon substrate 20 with N_2O gas before forming the HfO_2 film 22A.

[0093] In the process shown in Figure 7B, hydrogen (H) contained in the Hf source is spontaneously captured in the HfO_2 film 22A. On the other hand, carbon (C) contained in the Hf source is oxidized by the O_2 gas as an oxidizing agent, so that it is exhausted in the form of CO or CO_2 from the chamber. In the chamber, in addition to Hf, O, C, and H, which are constituent elements of the Hf source, N_2 gas is present, but the N_2 gas is very inert at temperatures below about 500 °C, so that an influence of the N_2 gas can be ignored.

[0094] When the HfO_2 film 22A was analyzed by a SIMS method (secondary ion mass spectroscopy), it was found that primary elements constituting the HfO_2 film 22A were Hf and O. In the HfO_2 film 22A, 3×10^{19} to 4×10^{20} carbon atoms/cm³ and 5×10^{20} to 4×10^{21} hydrogen atoms/cm³ were contained.

[0095] Next, a heat treatment (hereinafter, referred to as PDA (post deposition anneal)) is performed with respect to the HfO_2 film 22A. PDA is performed, for example, in a nitrogen atmosphere at about 700°C for 30 seconds. Now, changes occurring in the stacked structure of the SiON film 21B and the HfO_2 film 22A by performing PDA will be described in detail with reference to Figures 9A to 9D. As described above, before performing PDA, as shown in Figure 9A, the SiON film 21B and the HfO_2 film 22A contain hydrogen. When PDA is performed, as shown in Figure 9B, hydrogen is desorbed from the SiON film 21B and the HfO_2 film 22A efficiently in the form of hydrogen gas. As a result, as shown in Figure 9C, vacancies (white circles in Figure 9C) are formed in the SiON film 21B and the HfO_2 film 22A. Then, as shown in Figure 9D, silicon contained in the silicon substrate 20 or the SiON film 21B is diffused into the HfO_2 film 22A through the vacancies, and Hf contained in the HfO_2 film 22A is diffused into the SiON film 21B. As a result, as shown in Figure 7C, a silicon-containing HfO_2 film 22 having high thermal stability is formed, and a lower barrier film 21 made of the Hf-containing SiON film having a high relative dielectric constant can be formed. The silicon-containing HfO_2 film 22 is formed by making the HfO_2 film 22A dense by the diffusion of silicon. The specific composition of the lower

barrier film 21 is the same as the lower barrier film 11b of the first embodiment.

[0096] In other words, vacancies obtained by desorbing hydrogen from the HfO_2 film 22A and the SiON film 21B has the effect of promoting mutual diffusion of Hf and Si. In this case, setting the temperature for PDA to about 700 °C brings about double effects, that is, an effect of promoting hydrogen desorption to facilitate formation of vacancies and an effect of facilitating diffusion of Hf or Si. As a result, one PDA allows Si to be captured in the HfO_2 film 22A to form the silicon-containing HfO_2 film 22 having high thermal stability, and allows Hf to be captured in the SiON film 21B to form the lower barrier film 21 (Hf-containing SiON film) having a high relative dielectric constant. Therefore, the thermal stability of a gate insulating film 25 (see Figure 8C) as a whole including the silicon-containing HfO_2 film 22 and the lower barrier film 21 can be improved, and consequently the relative dielectric constant of the gate insulating film 25 as a whole can be increased.

[0097] Next, the surface of the silicon-containing HfO_2 film 22 is nitrided lightly, so that as shown in Figure 8A, an upper barrier film 23 with a thickness of about 2 nm having a high relative dielectric constant is formed. That is to say, the upper barrier film 23 is formed of the silicon-containing HfO_2 film containing nitrogen. The specific composition of the upper barrier film 23 is the same as that of the upper barrier film 11c of the first embodiment.

[0098] Next, as shown in Figure 8B, a polysilicon film 24 serving as a gate electrode is formed on the upper barrier film 23 by, for example, CVD. Thereafter, the polysilicon film 24, the upper barrier film 23, the silicon-containing HfO_2 film 22, and the lower barrier film 21 are dry-etched sequentially, using a mask pattern (not shown) covering a gate electrode formation region. Thus, as shown in Figure 8C, a gate electrode 26 is formed on the silicon substrate 20 via the gate insulating film 25 having a stacked structure of the lower barrier film 21, the silicon-containing HfO_2 film 22, and the upper barrier film 23. Thereafter, ions are implanted into the silicon substrate 20 with the gate electrode 26 as a mask, so that an impurity diffusion layer 27 serving as a source region or a drain region is formed. Finally, in order to activate impurities in the impurity diffusion layers 27, a heat treatment is performed at about 950°C for about 30 minutes. The processes described above provide a MIS electric field effect transistor having the high-k gate insulating film.

[0099] As described above, according to the second embodiment, the HfO_2 film 22A containing hydrogen is formed on the silicon substrate 20, and then a heat treatment (PDA) is performed with respect to the HfO_2 film 22A to desorb hydrogen, and silicon is diffused in the HfO_2 film 22A through the thus formed vacancies so that the silicon-containing HfO_2 film 22 is formed. For this reason, it is possible to allow silicon to be contained efficiently in the HfO_2 film 22A and the vacancies eventually disappear so that the silicon-containing HfO_2 film 22

becomes dense. In this case, as described in the first embodiment, the silicon-containing HfO_2 film 22 is hardly crystallized by a high temperature in the production process, so that the silicon-containing HfO_2 film 22 remains mostly amorphous even after a device is complete. As a result, leak current can be suppressed from occurring in the gate insulating film 25 having the silicon-containing HfO_2 film 22, that is, the high-k gate insulating film. Therefore, the thermal stability of the high-k gate insulating film is improved, so that a semiconductor device having excellent heat resistance can be realized and the process margin in the production of a semiconductor device can be increased.

[0100] Furthermore, according to the second embodiment, before forming the HfO_2 film 22A, the Si_3N_4 film 21A containing hydrogen is formed on the silicon substrate 20. The Si_3N_4 film 21A is oxidized when forming the HfO_2 film 22A and turns into the SiON film 21B. Thereafter, when the HfO_2 film 22A is subjected to PDA, silicon contained in the SiON film 21B is diffused into the HfO_2 film 22A. Moreover, hydrogen is desorbed from the SiON film 21B to form vacancies, and Hf contained in the HfO_2 film 22A is diffused into the SiON film 21B through the vacancies, so that the lower barrier film 21 is formed. Therefore, it is ensured that silicon can be contained in the HfO_2 film 22A. Furthermore, the HfO_2 film 22A or the silicon-containing HfO_2 film 22 can be prevented from being reacted with the silicon substrate 20. Furthermore, the lower barrier film 21 contains the same metal, Hf as in the silicon-containing HfO_2 film 22, so that the relative dielectric constant of the lower barrier film 21 can be high, and thus the relative dielectric constant of the gate insulating film 25 as a whole can be high.

[0101] Moreover, according to the second embodiment, the upper barrier film 23 is formed by nitriding the surface of the silicon-containing HfO_2 film 22 in a process between the process for performing PDA to the HfO_2 film 22A and the process for forming the polysilicon film 24 serving as the gate electrode 26. Therefore, the material of the gate electrode 26 and material of the silicon-containing HfO_2 film 22 are prevented from diffusing each other. Furthermore, the upper barrier film 23 contains the same metal, Hf as in the silicon-containing HfO_2 film 22, so that the relative dielectric constant of the upper barrier film 23 can be high, and thus the relative dielectric constant of the gate insulating film 25 as a whole can be high.

[0102] Furthermore, according to the second embodiment, the HfO_2 film 22A is formed by CVD that employs a source precursor containing hafnium and hydrogen, so that it is ensured that hydrogen can be contained in the HfO_2 film 22A.

[0103] Hereinafter, the features (e.g., mutual diffusion of Hf and Si by hydrogen desorption) and the effect (e.g., improvement of thermal stability) of the process of performing PDA to the HfO_2 film 22A will be described with reference to the drawings showing experiment data

or the like.

[0104] Figure 10 shows the result of measurement by TDS (thermal desorption spectroscopy) regarding hydrogen that is being desorbed from the HfO_2 film by a heat treatment. In Figure 10, the horizontal axis shows the heat treatment temperature and the vertical axis shows the spectrum intensity of hydrogen gas measured by TDS. As shown in Figure 10, when the heat treatment temperature reaches about 400°C , first, hydrogen adsorbed on the surface of the HfO_2 film starts to be desorbed. Thereafter, when the heat treatment temperature reaches about 700°C , hydrogen contained in the HfO_2 film is desorbed. The density of hydrogen molecules that was contained in the HfO_2 film just after deposition and eventually desorbed from the HfO_2 film by a heat treatment was measured and found to be as high as 5.6×10^{20} molecules/cm². According to the results shown in Figure 10, when the heat treatment temperature is about 700°C , the detected amount of desorbed hydrogen is largest. Therefore, the optimal temperature for PDA is about 700°C , and the thus setting allows excessive hydrogen contained in the HfO_2 film to be desorbed so that the HfO_2 film can be made dense most effectively.

[0105] While performing a heat treatment (temperature increase rate of $10^\circ\text{C}/\text{min}$) in an ultrahigh vacuum with respect to a sample of the HfO_2 film formed on a Si substrate by CVD with Hf-t-butoxide, which is a liquid Hf source, the HfO_2 film that was being heated were subjected to in-situ observation to see its changes, using a high resolution cross-sectional TEM (transmission electron microscope), and the following was confirmed. At room temperature (immediately after the HfO_2 film is formed), an interface layer (corresponding to the SiON film 21B) that contains a large number of Si atoms and a small number of Hf atoms is present on the Si substrate, and the HfO_2 layer that contains a small number of Si atoms and a large number of Hf atoms is present on the interface layer. Thereafter, as the temperature increases, in the temperature range from 620°C to 850°C , a mutual diffusion layer that contains a smaller number of Si atoms than that of the interface layer and a smaller number of Hf atoms than that of the HfO_2 layer evidently starts to appear between the interface layer and the HfO_2 layer. Finally, when a high temperature annealing is performed at 860°C , the total physical thickness of a stacked structure (corresponding to the silicon-containing HfO_2 film 22) of the HfO_2 layer and the mutual diffusion layer is larger than that of the HfO_2 layer at the time of deposition (room temperature). That is to say, the interface layer is contracted by expansion of the mutual diffusion layer, and as a result, the relative dielectric constant of the entire Hf silicate stacked structure including the interface layer becomes high.

[0106] In the case of regular PDA, the temperature increase rate is as high as $50^\circ\text{C}/\text{sec}$, and the retention period at a heat treatment temperature of about 700°C is as short as 30 seconds, so that the thermal budget

(thermal load) is much smaller than that from the in-situ observation during heating by the high resolution cross-sectional TEM. Therefore, oxidation of the Si substrate caused by PDA occurs only 1 nm or less, and the interface layer becomes very thin because of the mutual diffusion of Si and Hf, so that the final interface layer (corresponding to the lower barrier film 21) is about 0.5 nm. Thus, the relative dielectric constant of the entire Hf silicate stacked structure including the interface layer becomes high, and as a result, the EOT of the stacked structure as a whole becomes very small. In other words, forming the HfO_2 film by CVD employing a Hf source containing hydrogen is very advantageous as a method for forming a high-k gate insulating film. On the other hand, a HfO_2 film is formed by CVD employing a regular Hf source free from hydrogen, and an in-situ observation during heating is performed with respect to the HfO_2 film with the high resolution cross-sectional TEM. Then, it was found that mutual diffusion hardly occurred between the interface layer and the HfO_2 layer. As a result, the thermal stability of the HfO_2 layer was not improved and the relative dielectric constant of the stacked structure of the interface layer and the HfO_2 layer was not increased.

[0107] Figure 11 shows the results of C-V measurement after the heat treatment with respect to the HfO_2 film containing hydrogen formed by CVD employing Hf-t-butoxide. More specifically, annealing for activating impurities implanted to the gate electrode was performed at 900°C, 950°C and 1050°C with respect to samples of a MOS capacitor employing a HfO_2 film having a physical thickness of 3.0 to 3.3 nm as the gate insulating film and polysilicon as the gate electrode. Then, a gate voltage V_g was applied with a voltage of 0 V set on the substrate side. In Figure 11, the horizontal axis shows the gate voltage (V_g) and the vertical axis shows the capacitance. ♦ shows the measured value of the capacitance when a heat treatment was performed at 900°C, ■ shows the measured value of the capacitance when a heat treatment was performed at 950°C, and ▲ shows the measured value of the capacitance when a heat treatment was performed at 1050°C.

[0108] As shown in Figure 11, when the HfO_2 film containing hydrogen formed of Hf-t-butoxide is used, stable C-V curve is shown even if the annealing temperature for activation is increased, and the temperature at which the sample can withstand as an ideal MOS capacitor is as high as 1050°C or more. In other words, in the HfO_2 film containing hydrogen, as a result of occurrence of significant mutual diffusion of Hf and Si accompanied by hydrogen desorption caused by PDA, a Si-containing layer is present on the surface side of the HfO_2 film. Therefore, also when polysilicon is used as the gate electrode, as shown in Figure 11, very stable heat resistance is exhibited at about 1050°C.

[0109] Figure 12 shows the result of C-V measurement after a heat treatment with respect to a HfO_2 film free from hydrogen formed by CVD employing a source

free from hydrogen, specifically, Hf-nitrato ($\text{Hf}(\text{NO}_3)_3$) as a comparative example. More specifically, annealing for activating impurities implanted to the gate electrode was performed at 900°C, 950°C and 1150°C with respect to samples of a MOS capacitor employing a HfO_2 film having a physical thickness of 3.0 to 3.3 nm as the gate insulating film and polysilicon as the gate electrode. Then, a gate voltage V_g was applied with a voltage of 0 V set on the substrate side. In Figure 12, the horizontal axis shows the gate voltage (V_g) and the vertical axis shows the capacitance. ■ shows the measured value of the capacitance when a heat treatment was performed at 900°C, ♦ shows the measured value of the capacitance when a heat treatment was performed at 950°C, and ▲ shows the measured value of the capacitance when a heat treatment was performed at 1150°C.

[0110] As shown in Figure 12, when the HfO_2 film free from hydrogen formed of Hf-nitrato is used, the temperature at which the sample can withstand as an ideal MOS capacitor is at most 900°C. Taking the results shown in both Figures 11 and 12 into consideration, the thermal stability guarantee temperature when the HfO_2 film containing hydrogen is used is 1050°C or more, whereas the thermal stability guarantee temperature when the HfO_2 film free from hydrogen is used is about 900°C. In other words, using the HfO_2 film containing hydrogen improves the thermal stability guarantee temperature by 150°C or more.

[0111] Figure 13 shows the results of comparison in the thermal stability between the case where a HfO_2 film containing hydrogen was used and the case where a HfO_2 film free from hydrogen was used in a MOS capacitor having a stacked structure of Si substrate / SiN film / HfO_2 film / polysilicon film. More specifically, annealing for activation was performed at temperatures in the range from 900°C to 1150°C for 30 seconds in a nitrogen atmosphere with respect to each MOS capacitor sample. Then, a gate voltage (V_g) of -1.0 V was applied with a voltage of 0 V set on the substrate side, and leak current J_g was measured. The HfO_2 film containing hydrogen was formed of Hf-t-butoxide, and the HfO_2 film free from hydrogen was formed of a source free from hydrogen. In Figure 13, the horizontal axis shows the activation annealing temperature, and the vertical axis shows the leak current J_g . ♦ shows the measured value of the leak current J_g when a source free from hydrogen is used, and □ shows the measured value of the leak current J_g when Hf-t-butoxide was used.

[0112] As shown in Figure 13, when the HfO_2 film containing hydrogen formed of Hf-t-butoxide was used and the annealing temperature for activation was increased, an increase of the leak current J_g could be restricted to only one order. On the other hand, in the case where the HfO_2 film free from hydrogen was used and the annealing temperature for activation was increased, the leak current J_g was increased by about three orders, that is, about 1000 times larger than in the case of the HfO_2 film containing hydrogen. In other words, using the

HfO₂ film containing hydrogen can reduce the defect production probability to about 1/1000 of that in the case where the HfO₂ film free from hydrogen.

[0113] Each of the HfO₂ film containing hydrogen and the HfO₂ film free from hydrogen was deposited on a silicon substrate to the same physical thickness (3 nm), and the EOT of the HfO₂ film including the interface layer was measured. The results were as follows. The EOT was 1.1 nm when the HfO₂ film containing hydrogen was deposited, and the EOT was 1.6 nm when the HfO₂ film free from hydrogen was deposited. That is to say, the relative dielectric constant when the HfO₂ film containing hydrogen was deposited was about 1.46 times higher than that when the HfO₂ film free from hydrogen was deposited. This is caused by the fact that when the HfO₂ film containing hydrogen was deposited, Si and Hf are diffused mutually between the interface layer and HfO₂ layer so that Hf is contained in the interface layer, and consequently the relative dielectric constant in the interface layer portion is reduced significantly.

[0114] A HfO₂ film containing hydrogen having a thickness of 3.5 nm was formed on a silicon substrate, and then a PDA treatment (800°C, 30 seconds) was performed with respect to the HfO₂ film. Thereafter, Si, O and Hf were measured from the surface side of the HfO₂ film by XPS (X-ray photoelectron spectroscopy) using MgK α radiation and the composition of the HfO₂ film after the PDA treatment was found to be 0.6 for Hf, 0.49 for Si and 2.0 for O. It should be noted that since primarily the surface of the HfO₂ film was observed for measurement by the XPS technique, the detection depth was set to about 2 to 3 nm by detecting photoelectrons having an escape angle of 57 degrees with respect to the surface of the substrate. The results as described above indicate that in the HfO₂ film after the PDA treatment, Si has been diffused up to the vicinity of the surface.

[0115] Figure 14 shows the relationship between the physical thickness of the HfO₂ film immediately after being formed and the leak current after a MOS capacitor was complete in the case where PDA was performed with respect to the HfO₂ film (containing hydrogen), which is the insulating film of the MOS capacitor. More specifically, after a HfO₂ film containing hydrogen was formed by CVD, PDA was performed to the HfO₂ film in a nitrogen atmosphere at pressure of about 60000 Pa (450 torr) at 800°C for 30 seconds. Thereafter, a polysilicon film that was to serve as a gate electrode was deposited. Then, after ions were implanted into the polysilicon film, annealing for activation is performed in a nitrogen atmosphere at a pressure of about 110000 Pa (760 torr) at 900°C for 30 seconds. Thereafter, a gate voltage (V_G) of -1.0 V was applied with 0 V on the substrate side, and the leak current J_G was measured. The physical thickness of the HfO₂ film immediately after being formed is measured by an ellipsometry method (polarization method). For comparison, with respect to samples of MOS capacitors obtained by omitting the process of performing PDA with respect to the HfO₂ film,

the relationship between the physical thickness of the HfO₂ film immediately after being formed and the leak current after the MOS capacitor was produced was investigated.

5 [0116] As shown in Figure 14, when PDA is performed, a smaller leak current J_G is achieved than when PDA is not performed. This seems to be caused for the reason as follows: Si is diffused to the HfO₂ film by the PDA, which prevents the HfO₂ film from being crystallized by annealing for activation, therefore the HfO₂ film in the finished MOS capacitor remains mostly amorphous, so that the gate leak current can be suppressed from increasing. Furthermore, it seems that the gate leak current has been reduced also by the fact that a reaction between the electrode material and the material of the high dielectric constant film has been suppressed by achieving a dense silicon-containing HfO₂ film. As shown in Figure 14, the effect of suppressing the gate leak current in the case where PDA is performed is exhibited more significantly as the physical thickness of the HfO₂ film is smaller. The above results have confirmed that it is very important to provide a process of performing PDA (post deposition anneal) with respect to the high dielectric constant film after the high dielectric constant film that will serve as a gate insulating film is deposited and before a gate electrode is formed in order to reduce the leak current effectively.

[0117] In the second embodiment, a polysilicon film 24 is used as the gate electrode 26, but a metal film can be used instead. For example, the surface of the silicon-containing HfO₂ film 22 is nitrided, and then a TiN film and an Al film that will serve as the gate electrode 26 may be deposited sequentially by sputtering. Alternatively, after the surface of the silicon-containing HfO₂ film 22 is nitrided, a Ta film that will serve as the gate electrode 26 may be deposited. Alternatively, a TiN film, a TaN film or the like may be deposited without nitriding the surface of the silicon-containing HfO₂ film 22. In this case, Si or Ge can be mixed with the TiN film, the TaN film or the like. When a metal film is used as the gate electrode 26 as described above, after the metal film is formed, defects in the gate insulating film 25 can be reduced further by further applying a heat treatment (PMA: post metalization anneal). When a C-V measurement is performed with respect to the thus formed MOS structure, it is confirmed that the amount of the defects in the insulating film and the corresponding hysteresis are reduced. A temperature of 700°C or more is effective as the temperature of PMA. When annealing is performed in a gas containing hydrogen at 450°C for about 30 minutes, the interface state in the gate insulating film 25 can be reduced.

[0118] In the second embodiment, a HfO₂ film is used as the high dielectric constant material constituting the gate insulating film 25, ZrO₂, TiO₂, Ta₂O₅, La₂O₃, CeO₂, Al₂O₃, or BST (barium strontium titanium oxide) can be used instead. Alternatively, ternary oxide such as Hf_xAl_yO₂, where x > 0 and y > 0) can be used. Alternatively,

tively, metal silicate in which Si atoms are contained in metal oxide as described above can be used. In any case, the effect of mutual diffusion in the high dielectric constant film containing hydrogen can be realized regardless of the composition or the constituent materials at the time of the deposition of the high dielectric constant film.

[0119] In the second embodiment, the HfO_2 film 22A is deposited by CVD employing Hf-t-butoxide, which is a liquid Hf source precursor. However, instead of this, when CVD is used, other Hf source precursors containing hydrogen and hafnium such as tetrakis diethylamido hafnium, (TDEAH: $\text{C}_{16}\text{H}_{40}\text{N}_4\text{Hf}$), tetrakis dimethylamino hafnium (TDMAH: $\text{C}_{16}\text{H}_{36}\text{HfO}_4$), or tetrakis 1-methoxy-2-methyl-2-propoxy hafnium ($\text{Hf}(\text{MMP})_4$: $\text{Hf}(\text{OC}(\text{CH}_3)_2\text{CH}_2\text{OCH}_3)_4$) can be used. Alternatively, a HfO_2 film can be formed by CVD employing a solid Hf source precursor such as Hf-nitrato ($\text{Hf}(\text{NO}_3)_4$) and a source gas containing hydrogen such as hydrogen gas. Alternatively, when PVD (physical vapor deposition) such as sputtering is used, a target containing hafnium can be used in an atmosphere containing hydrogen. More specifically, a hafnium target can be used in an atmosphere containing oxygen gas and argon gas to which hydrogen gas is added, or a hafnium oxide target can be used in an atmosphere containing argon gas to which hydrogen gas is added. Hydrogen gas is added for hydrogen to be captured in the high dielectric constant film (HfO_2 film).

[0120] In the second embodiment, hydrogen is captured in the HfO_2 film 22A or the Si_3N_4 film 21A as a predetermined substance (substance for vacancy formation), but instead of this, for example, chlorine, fluorine, or iodine can be captured using a halogen-based gas. Any substances can be used as the substance for vacancy formation, as long as it can be desorbed from the HfO_2 film 22A or the Si_3N_4 film 21A in the form of gas at a temperature of about 600 to 850°C and can promote the diffusion of Hf or Si through the thus formed vacancies. Furthermore, the substance for vacancy formation for the HfO_2 film 22A may be different from that for the Si_3N_4 film 21A.

[0121] In the second embodiment, the Si_3N_4 film 21A, that is, the lower barrier film 21 can be formed by performing, for example, thermal nitridation or plasma nitridation in a gas containing nitrogen with respect to the silicon substrate 20. Alternatively, the SiON film 21B can be directly formed by nitriding the surface of the silicon substrate 20 with N_2O gas before forming the HfO_2 film 22A without forming the Si_3N_4 film 21A. Alternatively, the high dielectric insulating film containing nitrogen that will become the lower barrier film 21 can be directly formed on the silicon substrate 20 by introducing a gas containing nitrogen in the early stage of the formation of the HfO_2 film 22A by evaporation.

[0122] In the second embodiment, the upper barrier film 23 can be formed by performing, for example, thermal nitridation or plasma nitridation in a gas containing

nitrogen with respect to the silicon-containing HfO_2 film 22. Alternatively, the upper barrier film 23 can be formed by nitriding the surface of the silicon-containing HfO_2 film 22 by introducing nitrogen gas in the early stage of the formation of the polysilicon film 24 that will serve as the gate electrode 26. Alternatively, the high dielectric insulating film containing nitrogen that will become the upper barrier film 23 can be formed on the side of the surface of the HfO_2 film 22A by introducing a gas containing nitrogen in the final stage of the formation of the HfO_2 film 22A by evaporation.

[0123] In the second embodiment, PDA is performed with respect to the HfO_2 film 22A to form the silicon-containing HfO_2 film 22, and then the upper barrier film 23 is formed by nitriding the surface of the silicon-containing HfO_2 film 22. However, instead of this, after the upper barrier film 23 is formed by nitriding the surface of the HfO_2 film 22A, PDA is performed with respect to the HfO_2 film 22A to form the silicon-containing HfO_2 film 22.

[0124] In the second embodiment, the entire stacked structure of the lower barrier film 21, the silicon-containing HfO_2 film 22 and the upper barrier film 23 may contain nitrogen.

[0125] In the second embodiment, it is preferable that in the process shown in Figure 7B, first, a source such as evaporated Hf-t-butoxide is supplied into a chamber, and then oxygen gas is supplied to the chamber, and thereafter the temperature in the chamber is increased from room temperature and kept in a predetermined temperature range of about 300 to 500°C. This makes it possible that Hf molecules are adsorbed rapidly on the silicon substrate 20 at a low temperature, so that the HfO_2 film 22A can be formed uniformly. Furthermore, the incubation time from the start of the supply of the source gas to the start of crystal growth of the HfO_2 film can be shortened. Furthermore, the interface layer (SiON film 21B) formed between the HfO_2 film 22A and the silicon substrate 20 can be thin.

[0126] In the second embodiment, it is preferable that the temperature for the heat treatment in PDA in the process shown in Figure 7C is 600°C or more and 850°C or less. This ensures that hydrogen can be desorbed from the HfO_2 film 22A and thus silicon can be diffused in the HfO_2 film 22A.

[0127] In the second embodiment, it is preferable to satisfy $T \leq 6.69 \cdot y/(x+y) + 749.4$, where the composition of the silicon-containing HfO_2 film 22 is expressed as $\text{Hf}_x\text{Si}_y\text{O}$, where $x > 0$, and $y > 0$, and the maximum temperature in the production process is expressed as T [°C]. This ensures the thermal stability of the gate insulating film 25 having the silicon-containing HfO_2 film 22. When the gate electrode 26 is made of a material containing silicon, it is preferable to satisfy $T \leq 6.69 \cdot y/(x+y) + 749.4$, and $y/(x+y) \leq 0.30$. This ensures the thermal stability and the reliability of the gate insulating film 25 having the silicon-containing HfO_2 film 22.

[0128] The invention may be embodied in other forms

without departing from the spirit or essential characteristics thereof. The embodiments disclosed in this application are to be considered in all respects as illustrative and not limiting. The scope of the invention is indicated by the appended claims rather than by the foregoing description, and all changes which come within the meaning and range of equivalency of the claims are intended to be embraced therein.

Claims

1. A semiconductor device, **characterized by comprising:**

a gate insulating film formed on a substrate;
and
a gate electrode formed on the gate insulating film;
the gate insulating film comprising:

a high dielectric constant film containing a metal, oxygen and silicon; and
a lower barrier film formed below the high dielectric constant film and containing the metal, oxygen, silicon and nitrogen.

2. The semiconductor device according to claim 1, **characterized in that**

the gate insulating film comprises an upper barrier film formed above the high dielectric constant film, and

the upper barrier film contains the metal, oxygen and nitrogen.

3. The semiconductor device according to claim 1, **characterized in that**

$$0.23 \leq y/(x+y) \leq 0.90$$

when a composition of the high dielectric constant film is expressed as M_xSi_yO , where M, O and Si represent the metal, oxygen and silicon, respectively, and $x > 0$ and $y > 0$.

4. The semiconductor device according to claim 1, **characterized in that**

$$0.23 \leq y/(x+y) \leq 0.30$$

when a composition of the high dielectric constant film is expressed as M_xSi_yO , where M, O and Si represent the metal, oxygen and silicon, respectively, and $x > 0$ and $y > 0$.

5. The semiconductor device according to claim 1,

characterized in that

$$x/(x+y) \geq 0.10$$

when the metal is hafnium or zirconium, and a composition of the lower barrier film is expressed as M_xSi_yON , where M, O, Si and N represent the metal, oxygen, silicon and nitrogen, respectively, and $x > 0$ and $y > 0$.

6. The semiconductor device according to claim 1, **characterized in that** the gate electrode is a metal gate electrode.

7. A method for producing a semiconductor device, **characterized by comprising the steps of:**

forming a high dielectric constant film containing a metal, oxygen and a predetermine substance on a substrate;

performing a heat treatment with respect to the high dielectric constant film to diffuse silicon from the side of the substrate into the high dielectric constant film, thereby forming a silicon-containing high dielectric constant film; and
forming a conductive film for serving as a gate electrode on the silicon-containing high dielectric constant film.

8. The method for producing a semiconductor device according to claim 7, **characterized in that** the predetermined substance is hydrogen.

9. The method for producing a semiconductor device according to claim 7, **characterized in that** the metal is hafnium or zirconium.

10. The method for producing a semiconductor device according to claim 7, **characterized by comprising** forming an insulating film containing silicon, nitrogen and the predetermined substance on the substrate before the step of forming the high dielectric constant film; and

wherein the step of performing a heat treatment with respect to the high dielectric constant film comprises diffusing silicon contained in the insulating film into the high dielectric constant film, and forming a lower barrier film by diffusing the metal contained in the high dielectric constant film into the insulating film.

11. The method for producing a semiconductor device according to claim 7, **characterized in that**

the step of forming the high dielectric constant film comprises forming the high dielectric constant film by CVD employing a source precursor containing the metal and the predetermined substance.

12. The method for producing a semiconductor device according to claim 7, **characterized in that** the step of forming the high dielectric constant film comprises forming the high dielectric constant film by CVD employing a source precursor containing the metal and a source gas containing the predetermined substance.
13. The method for producing a semiconductor device according to claim 7, **characterized in that** the step of forming the high dielectric constant film comprises forming the high dielectric constant film by PVD employing a target containing the metal in an atmosphere containing the predetermined substance.
14. The method for producing a semiconductor device according to claim 7, **characterized by** comprising the step of forming an upper barrier by nitriding a surface of the silicon-containing high dielectric constant film between the step of performing a heat treatment with respect to the high dielectric constant film and the step of forming a conductive film.
15. The method for producing a semiconductor device according to claim 7, **characterized by** comprising the step of forming an upper barrier by nitriding a surface of the high dielectric constant film between the step of forming a high dielectric constant film and the step of performing a heat treatment with respect to the high dielectric constant film.
16. The method for producing a semiconductor device according to claim 7, **characterized in that** a temperature for the heat treatment in the step of performing the heat treatment with respect to the high dielectric constant film is 600°C or more and 850°C or less.
17. The method for producing a semiconductor device according to claim 7, **characterized in that**
- $$T \leq 6.69 \cdot y/(x+y) + 749.4,$$
- when a composition of the silicon-containing high dielectric constant film is expressed as $M_xSi_yO_z$, where M, O and Si represent the metal, oxygen and silicon, respectively, and $x > 0$ and $y > 0$, and a maximum temperature in a production process is expressed as T [°C].
18. The method for producing a semiconductor device according to claim 17, **characterized in that** the gate electrode is made of a material containing silicon, and
- $$y/(x+y) \leq 0.30.$$
19. The method for producing a semiconductor device according to claim 7, **characterized in that** the gate electrode is a metal gate electrode, the method comprising the step of performing a heat treatment with respect to the substrate after the step of forming a conductive film.
20. A method for producing a semiconductor device, **characterized by** comprising the steps of:
- forming a high dielectric constant film containing a metal, oxygen and hydrogen on a substrate;
 - performing a heat treatment with respect to the high dielectric constant film to diffuse silicon from the side of the substrate into the high dielectric constant film, thereby forming a silicon-containing high dielectric constant film; and
 - forming a conductive film for serving as a gate electrode on the silicon-containing high dielectric constant film.
21. The method for producing a semiconductor device according to claim 20, **characterized in that** the metal is hafnium or zirconium.
22. The method for producing a semiconductor device according to claim 20, **characterized by** comprising forming an insulating film containing silicon, nitrogen and hydrogen on the substrate before the step of forming the high dielectric constant film; and wherein the step of performing a heat treatment with respect to the high dielectric constant film comprises diffusing silicon contained in the insulating film into the high dielectric constant film, and forming a lower barrier film by diffusing the metal contained in the high dielectric constant film into the insulating film.
23. The method for producing a semiconductor device according to claim 20, **characterized in that** the step of forming the high dielectric constant film comprises forming the high dielectric constant film by CVD employing a source precursor containing the metal and hydrogen.
24. The method for producing a semiconductor device according to claim 20, **characterized in that** the step of forming the high dielectric constant film comprises forming the high dielectric constant film by CVD employing a source precursor containing the metal and a source gas containing hydrogen.
25. The method for producing a semiconductor device

according to claim 20, **characterized in that**
the step of forming the high dielectric constant
film comprises forming the high dielectric constant
film by PVD employing a target containing the metal
in an atmosphere containing hydrogen.

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26. The method for producing a semiconductor device
according to claim 20, **characterized by** compris-
ing the step of forming an upper barrier by nitriding
a surface of the silicon-containing high dielectric
constant film between the step of performing a heat
treatment with respect to the high dielectric con-
stant film and the step of forming a conductive film.

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27. The method for producing a semiconductor device
according to claim 20, **characterized by** compris-
ing the step of forming an upper barrier by nitriding
a surface of the high dielectric constant film be-
tween the step of forming a high dielectric constant
film and the step of performing a heat treatment with
respect to the high dielectric constant film.

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28. The method for producing a semiconductor device
according to claim 20, **characterized in that**
a temperature for the heat treatment in the
step of performing the heat treatment with respect
to the high dielectric constant film is 600°C or more
and 850°C or less.

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29. The method for producing a semiconductor device
according to claim 20, **characterized in that**

30

$$T \leq 6.69 \cdot y/(x+y) + 749.4,$$

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when a composition of the silicon-containing
high dielectric constant film is expressed as
 M_xSi_yO , where M, O and Si represent the metal,
oxygen and silicon, respectively, and $x > 0$ and $y > 0$,
and a maximum temperature in a production
process is expressed as T [°C].

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30. The method for producing a semiconductor device
according to claim 29, **characterized in that**
the gate electrode is made of a material con-
taining silicon, and

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$$y/(x+y) \leq 0.30.$$

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31. The method for producing a semiconductor device
according to claim 20, **characterized in that**
the gate electrode is a metal gate electrode,
and
the method comprising the step of performing
a heat treatment with respect to the substrate after
the step of forming a conductive film.

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Fig. 1

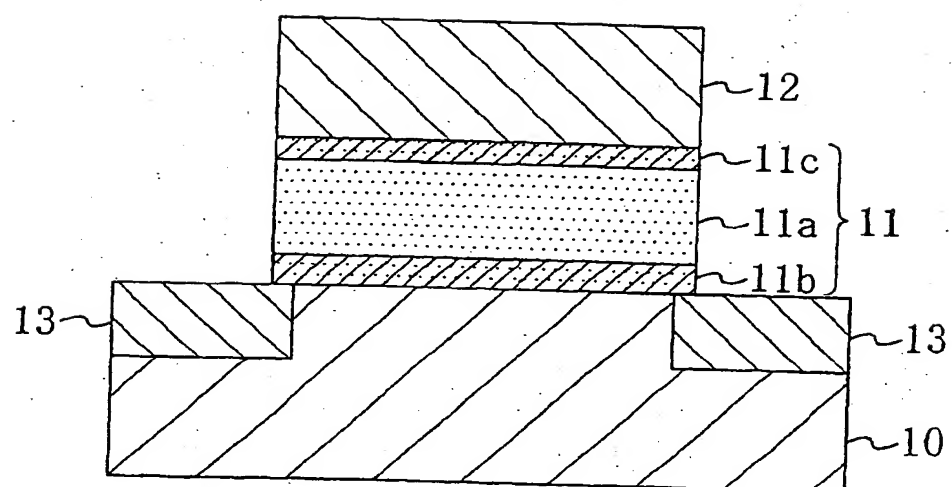


Fig. 2

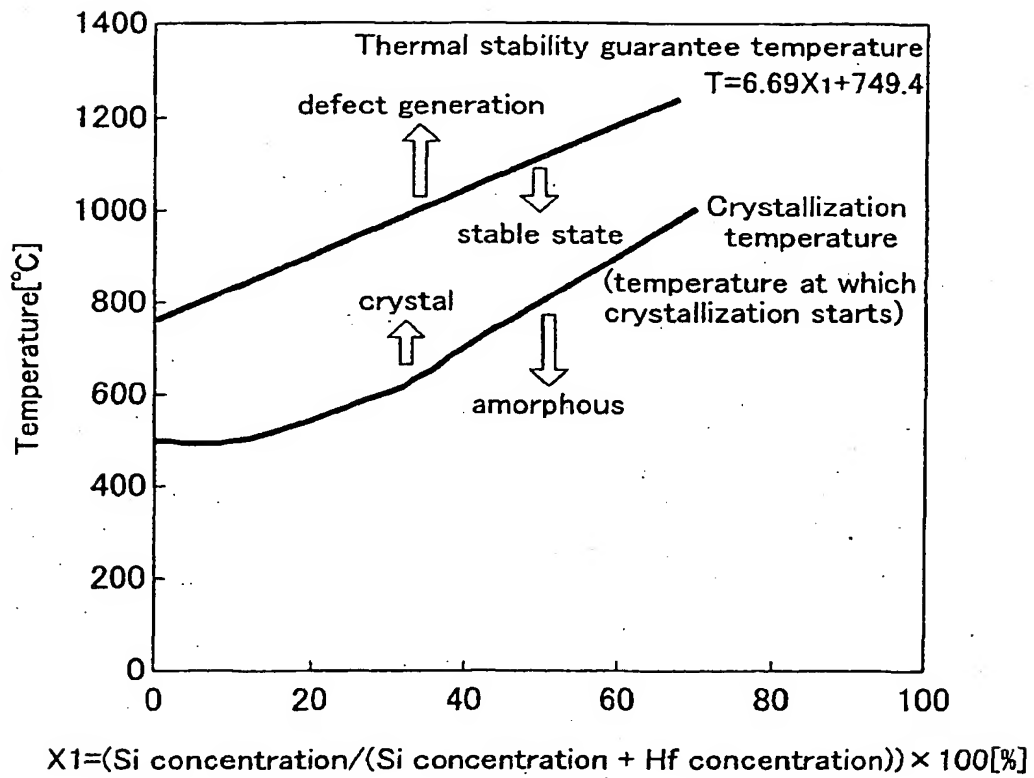


Fig. 3

A	B
750	≥ 0.1
800	≥ 7.6
850	≥ 15.0
900	≥ 23.0
950	≥ 30.0
1000	≥ 37.5
1050	≥ 45.0
1100	≥ 52.4

A:Maximum process temperature

B:Practical range of

$(\text{Si concentration} / (\text{Si concentration} + \text{Hf concentration})) \times 100[\%]$,
in which the thermal stability of Hf silicate can be ensured.

Fig. 4

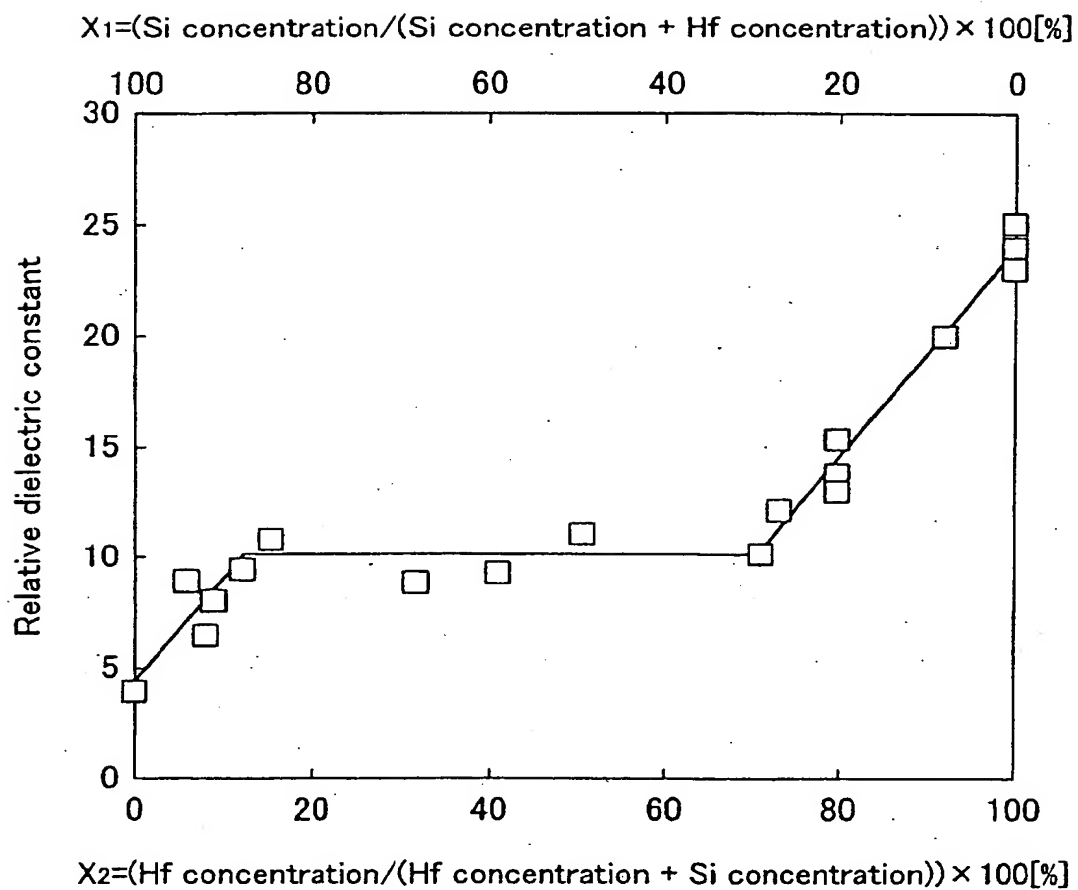
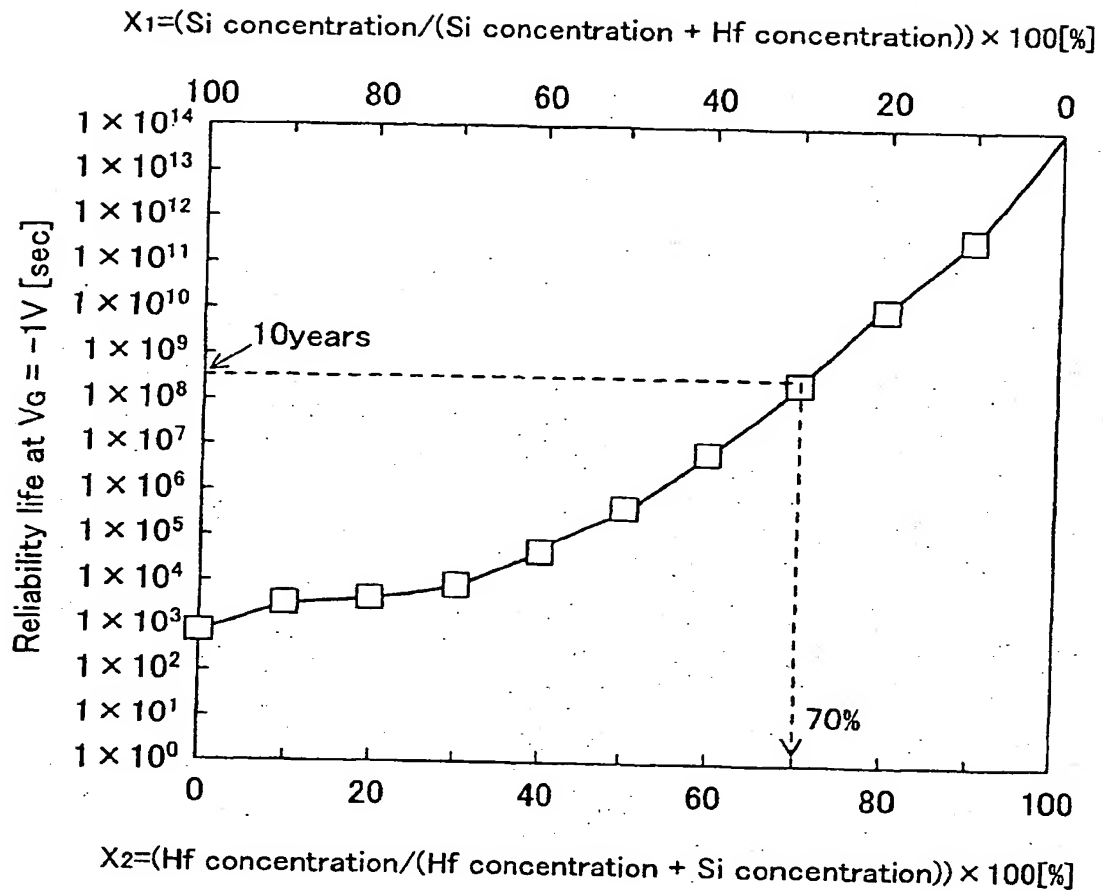


Fig. 5



Eox(real)model
 EOT=1.5nm
 Incidence of failure=100ppm
 MOS area =0.1cm²
 Temperature=100°C

Fig. 6

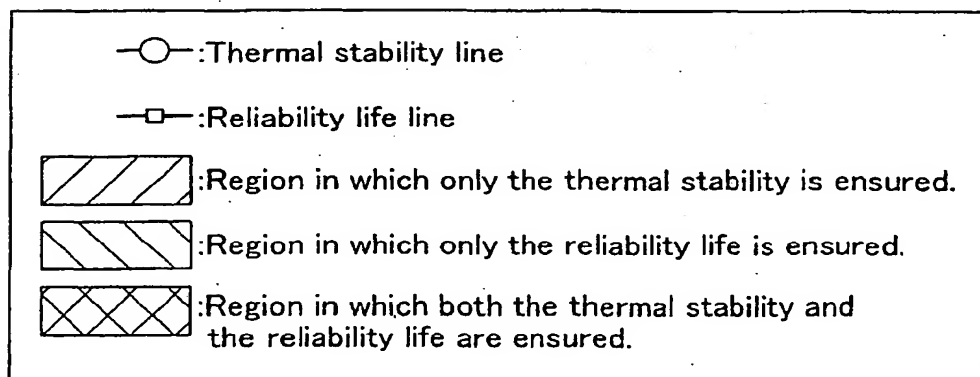
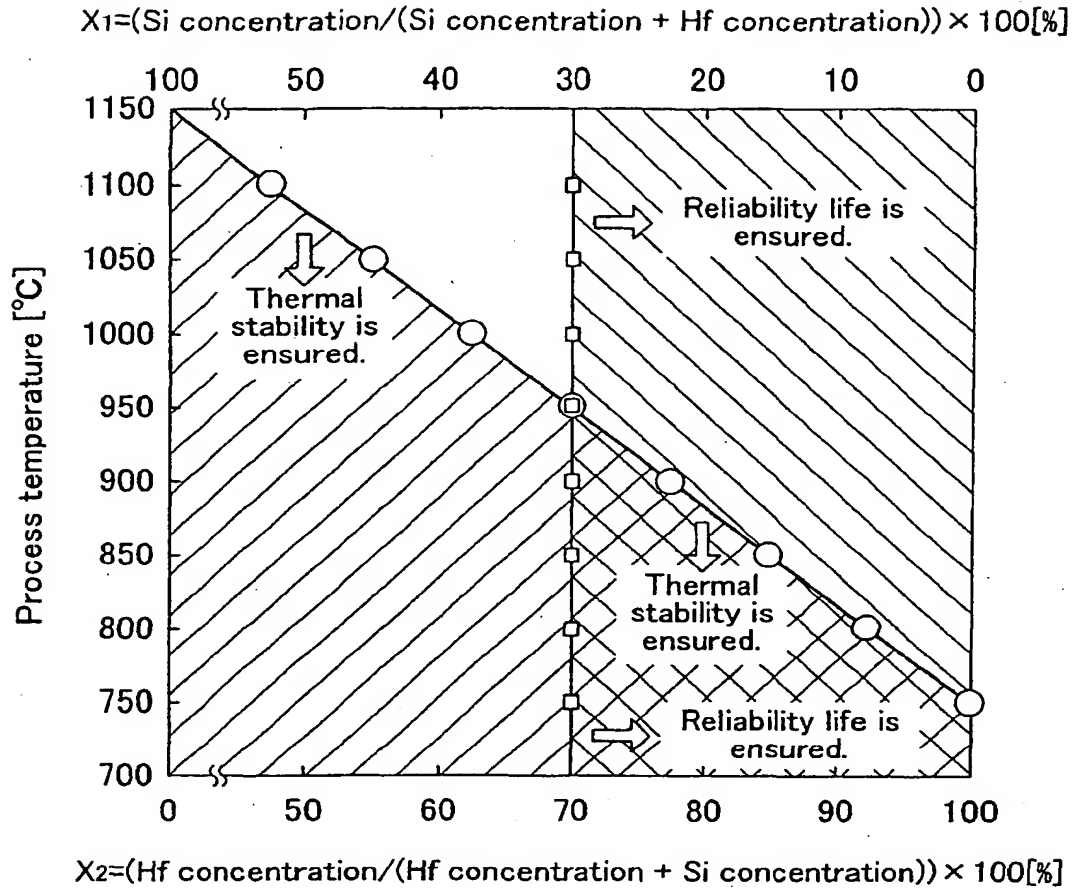


Fig. 7(a)

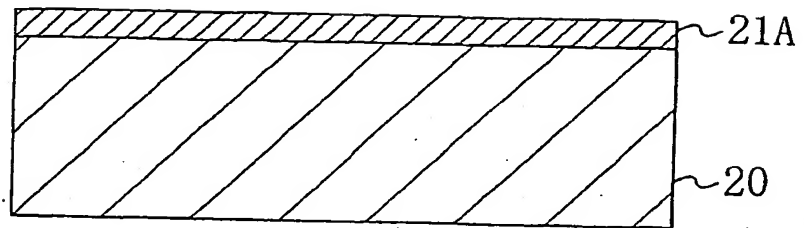


Fig. 7(b)

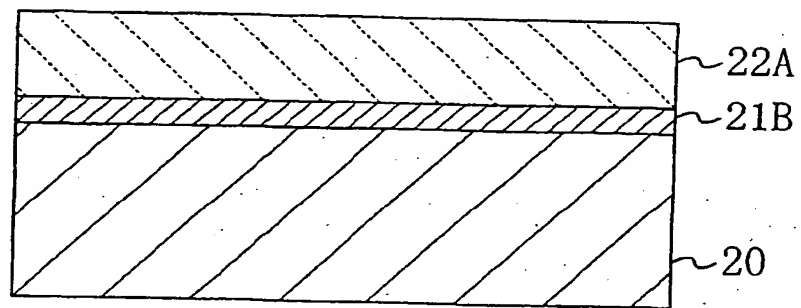


Fig. 7(c)

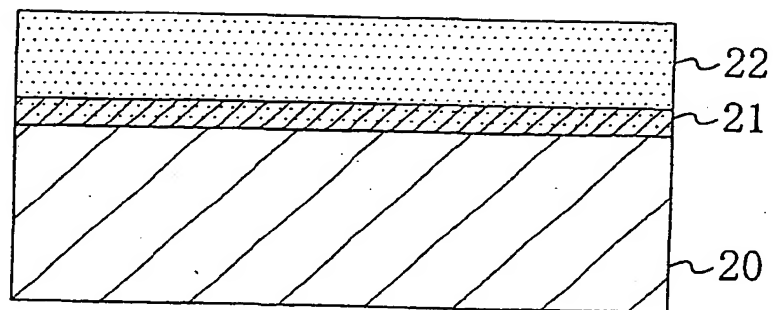


Fig. 8(a)

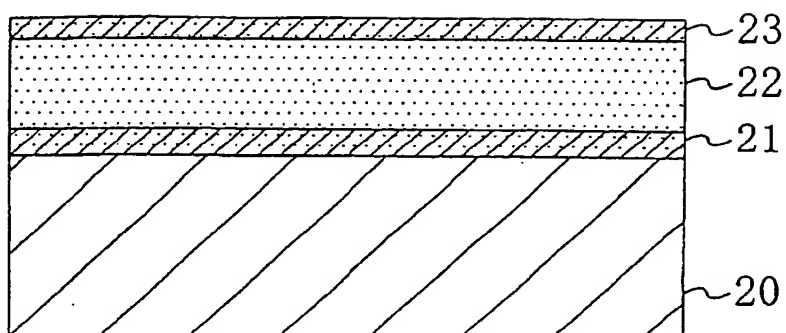


Fig. 8(b)

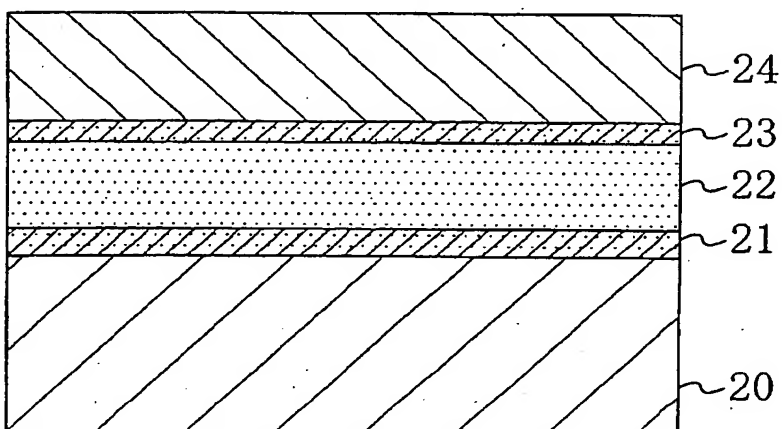


Fig. 8(c)

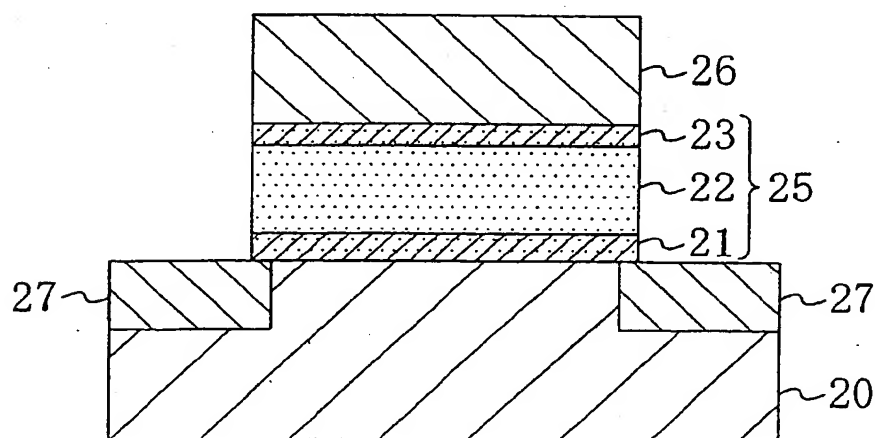


Fig. 9(a)

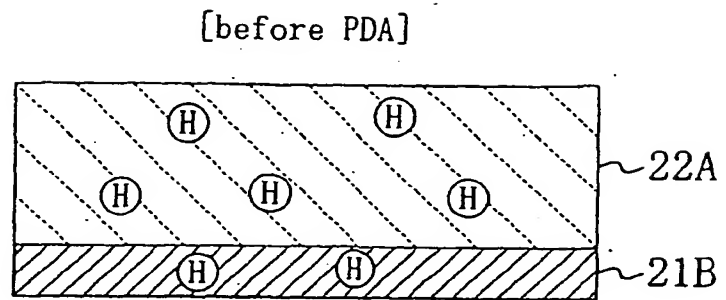


Fig. 9(b)

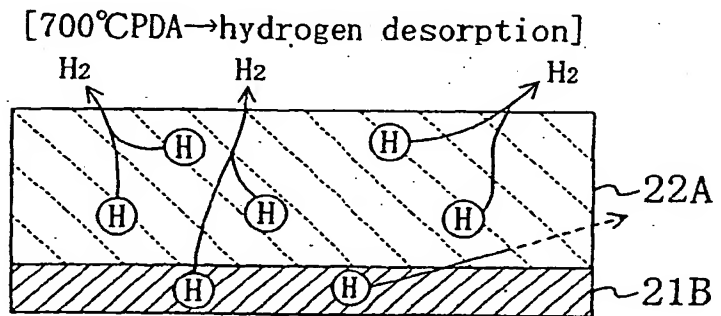


Fig. 9(c)

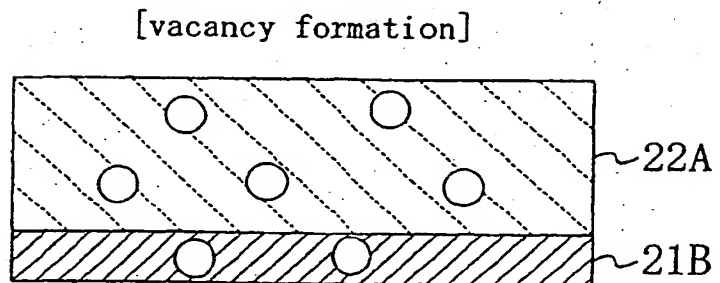


Fig. 9(d)

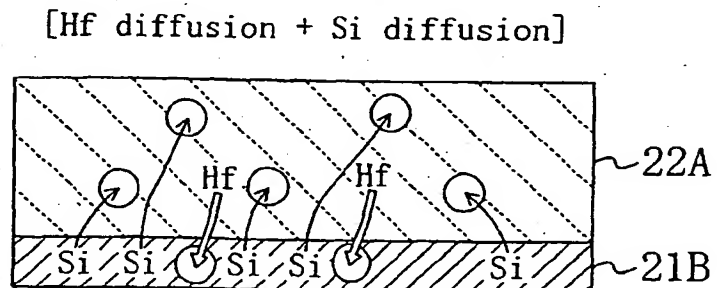


Fig. 10

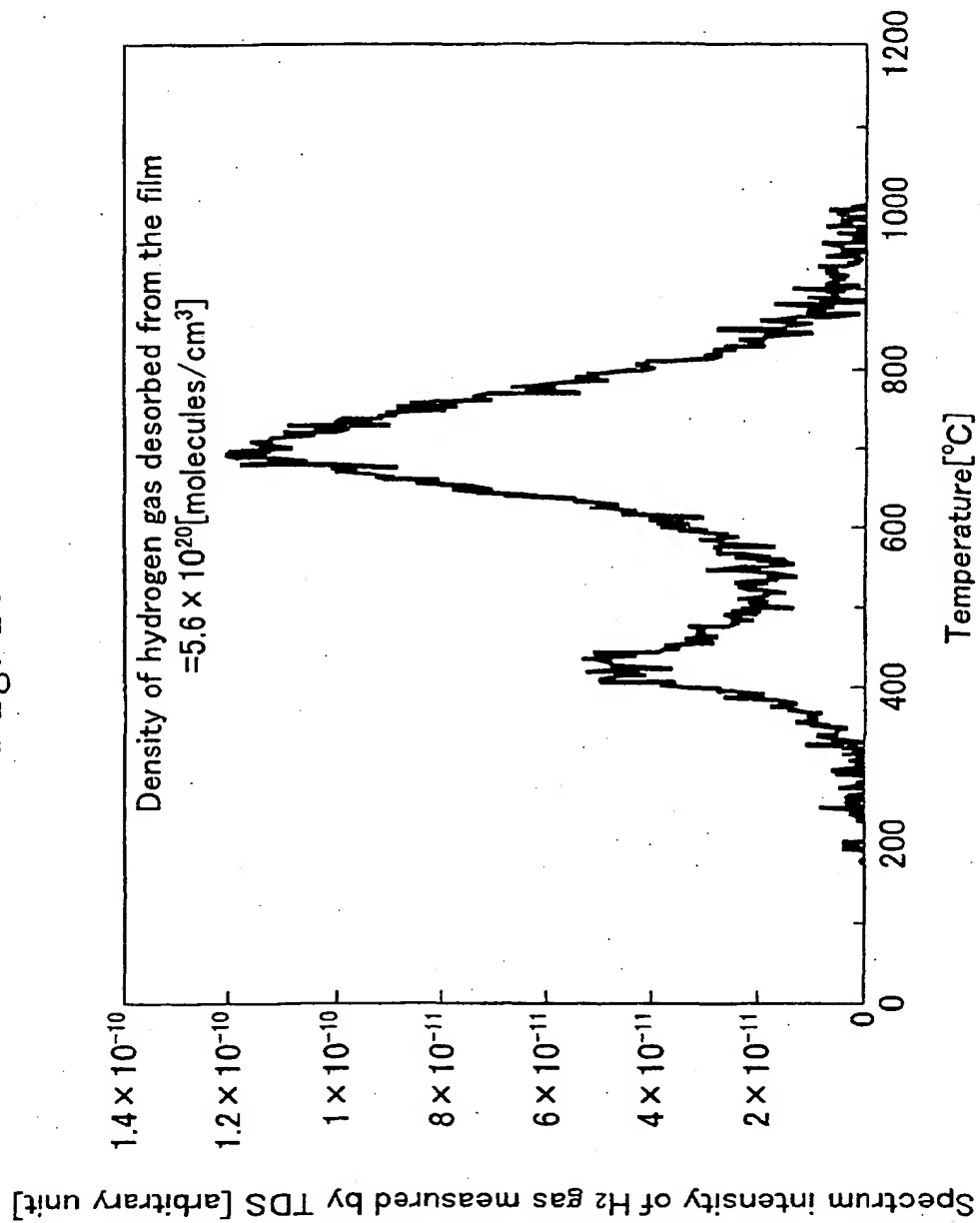


Fig. 11

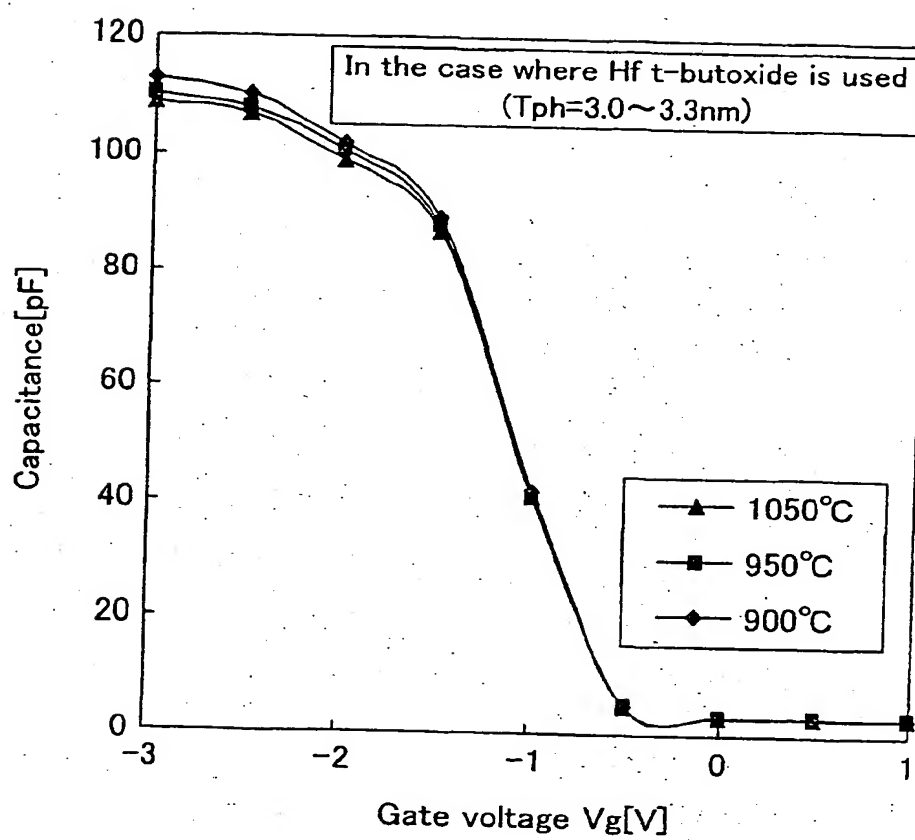


Fig. 12

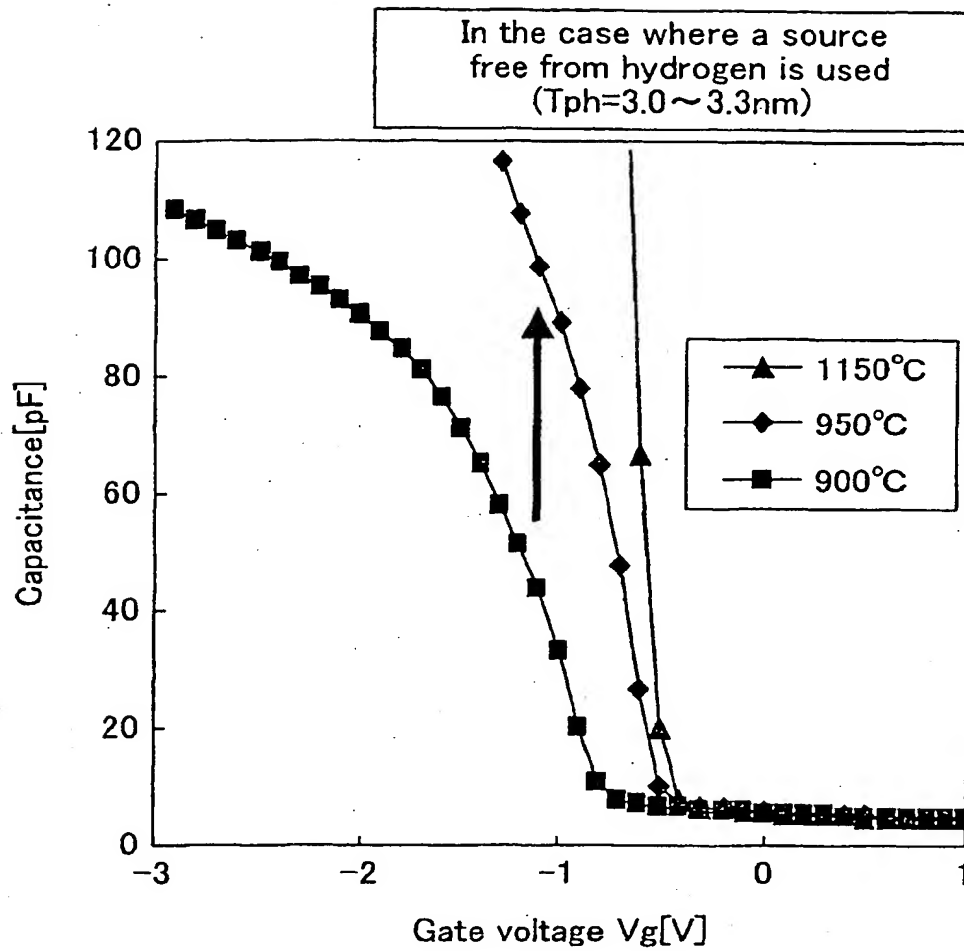


Fig. 13

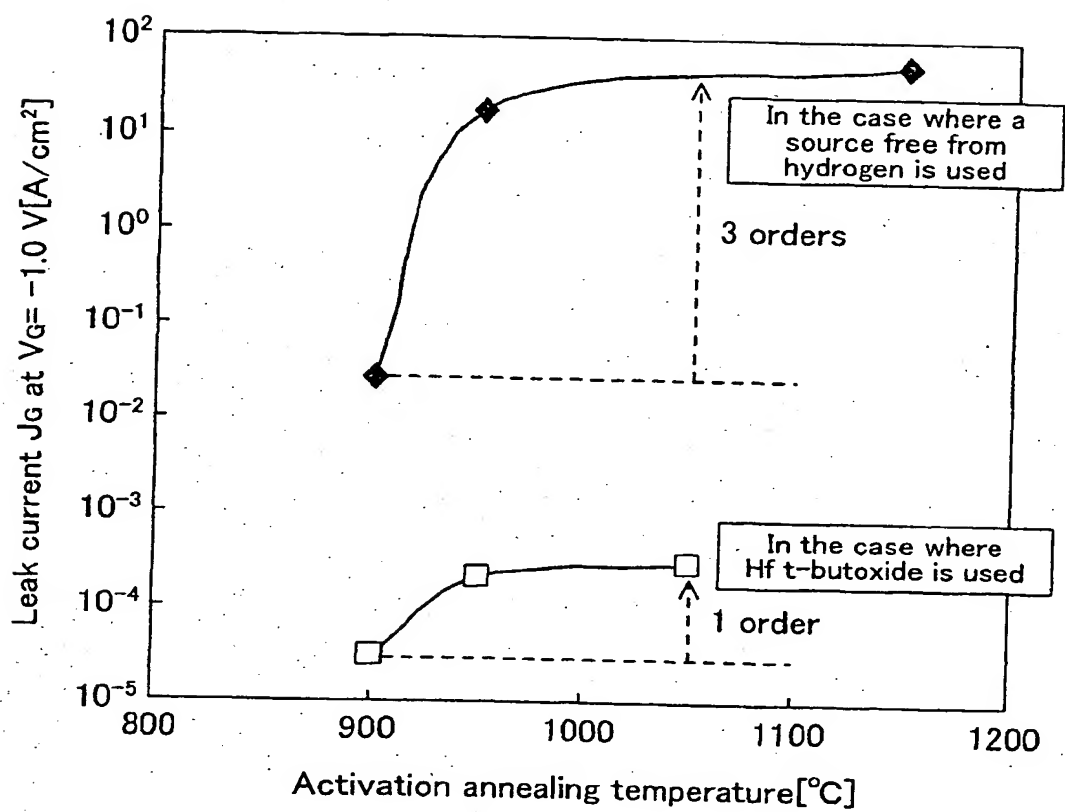
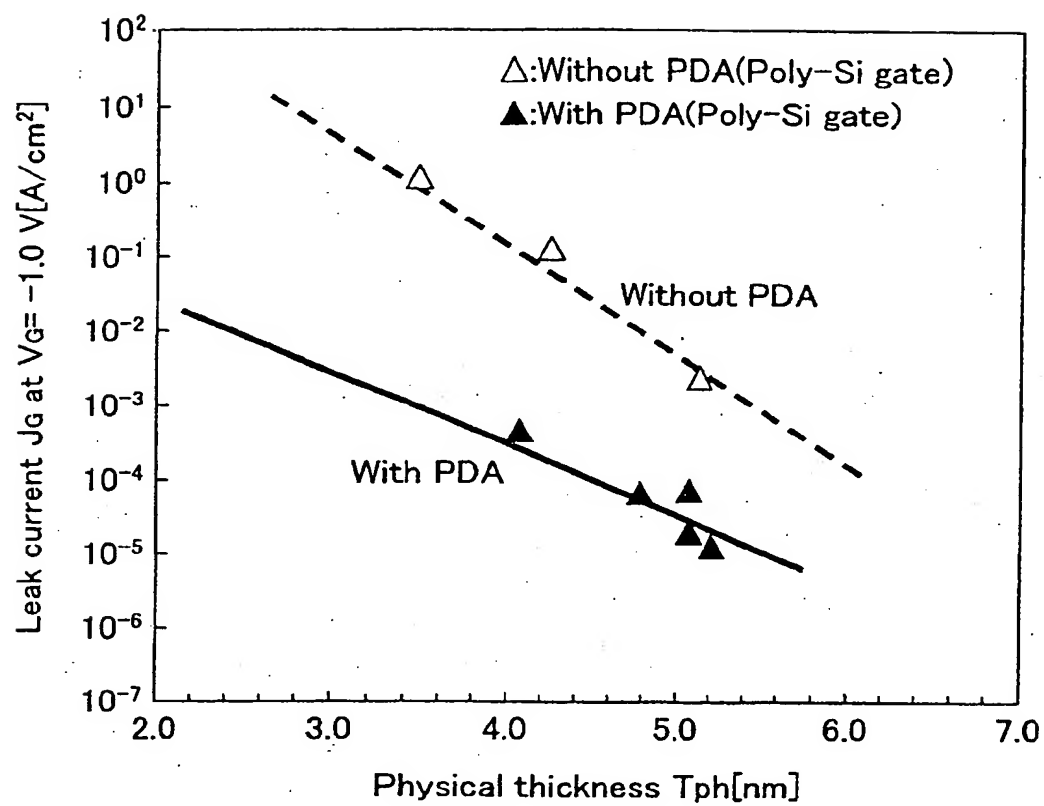


Fig. 14



INTERNATIONAL SEARCH REPORT

International application No.

PCT/JP02/05992

A. CLASSIFICATION OF SUBJECT MATTER Int.Cl ⁷ H01L29/78, H01L21/336, H01L21/316		
According to International Patent Classification (IPC) or to both national classification and IPC		
B. FIELDS SEARCHED Minimum documentation searched (classification system followed by classification symbols) Int.Cl ⁷ H01L29/78, H01L21/336, H01L21/316		
Documentation searched other than minimum documentation to the extent that such documents are included in the fields searched Jitsuyo Shinan Koho 1966-1996 Toroku Jitsuyo Shinan Koho 1996-2002 Kokai Jitsuyo Shinan Koho 1971-2002 Jitsuyo Shinan Toroku Koho 1994-2002		
Electronic data base consulted during the international search (name of data base and, where practicable, search terms used)		
C. DOCUMENTS CONSIDERED TO BE RELEVANT		
Category*	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No.
Y	EP 1108805 A1 (Motorola, Inc.), 20 June, 2001 (20.06.01),	1-6
A	Full text; Figs. 1 to 15 & JP 2001-223211 A Full text; Figs. 1 to 15	7-31
Y	US 6013553 A (Texas Instruments Inc.), 11 January, 2000 (11.01.00),	1-6
A	Full text; Figs. 1 to 12 & US 6020243 A Full text; Figs. 1 to 19 & JP 11-94094 A Full text; Figs. 1 to 20	7-31
<input checked="" type="checkbox"/> Further documents are listed in the continuation of Box C. <input type="checkbox"/> See patent family annex.		
* Special categories of cited documents: "A" document defining the general state of the art which is not considered to be of particular relevance "E" earlier document but published on or after the international filing date "L" document which may throw doubts on priority claim(s) or which is cited to establish the publication date of another citation or other special reason (as specified) "O" document referring to an oral disclosure, use, exhibition or other means "P" document published prior to the international filing date but later than the priority date claimed "T" later document published after the international filing date or priority date and not in conflict with the application but cited to understand the principle or theory underlying the invention "X" document of particular relevance; the claimed invention cannot be considered novel or cannot be considered to involve an inventive step when the document is taken alone "Y" document of particular relevance; the claimed invention cannot be considered to involve an inventive step when the document is combined with one or more other such documents, such combination being obvious to a person skilled in the art "Z" document member of the same patent family		
Date of the actual completion of the international search 25 July, 2002 (25.07.02)		Date of mailing of the international search report 06 August, 2002 (06.08.02)
Name and mailing address of the ISA/ Japanese Patent Office		Authorized officer
Facsimile No.		Telephone No.

Form PCT/ISA/210 (second sheet) (July 1998)

INTERNATIONAL SEARCH REPORT

International application No.

PCT/JP02/05992

C (Continuation). DOCUMENTS CONSIDERED TO BE RELEVANT

Category*	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No.
Y	EP 1028458 A (Texas Instruments Inc.), 16 August, 2000 (16.08.00),	1-6
A	Full text; Figs. 1 to 2 & JP 2000-208508 A Full text; Figs. 1 to 2	7-31
Y	Wilk, G.D. and Wallace, R.M. Electrical properties of hafnium silicate gate dielectrics deposited	1-6
A	directly on silicon. APPLIED PHYSICS LETTERS 10 May, 1999 (10.05.99), Vol.74, No.19, pages 2854 to 2856	7-31
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